CC2674R10

CC2674R10SimpleLink™ 高性能マルチプロトコル 2.4GHz ワイヤレス マイコン

1 特長

ワイヤレス マイクロコントローラ

- 強力な 48MHz Arm® Cortex®-M33 プロセッサと TrustZone® の組み合わせ
- FPUとDSPの拡張機能
- 1024kB フラッシュ プログラム メモリ
- 8kB のキャッシュ SRAM
- 高信頼性動作に適した 256kB の超低リーク SRAM (パリティ付き)
 - パリティが無効になっている場合は 32kB の SRAM を追加可能
- ダイナミック マルチプロトコル マネージャ (DMM) ドラ イバ
- プログラマブルな無線機能には、2-(G)FSK、4-(G)FSK, MSK, Bluetooth® 5.3 Low Energy, IEEE 802.15.4 PHY、MAC のサポートが含まれます
- OTA (Over-the-air) 更新をサポート

超低消費電力センサ コントローラ

- 4kB の SRAM を備えた自律型 MCU
- センサデータのサンプリング、保存、処理
- 高速ウェークアップによる低消費電力動作
- ソフトウェア定義ペリフェラル、静電容量式タッチ、流量 計、LCD

低消費電力

- MCU の消費電流:
 - 4.0mA のアクティブ モード電流、CoreMark®
 - 83µA/MHz (CoreMark® 実行中)
 - 1.19µA (スタンバイ モード、RTC、256kB SRAM)
 - 0.13µA (シャットダウン モード、ウェークアップ オン ピン)
- 超低消費電力センサコントローラの消費電流
 - 2MHz モードで 32µA
 - 24MHz モードで 849µA
- 無線の消費電流:
 - 2.4GHz で 6.4mA RX
 - 2.4GHz、0dBm で 7.3mA TX

無線プロトコルのサポート

- Thread、Zigbee®、Matter
- Bluetooth® 5.3 Low Energy
- **6LoWPAN**
- 独自システム

髙性能の無線

–104dBm (Bluetooth® Low Energy, 125kbps)

 –105dBm (IEEE 802.15.4-2006 2.4GHz OQPSK) コヒーレント モデム)

法規制の順守

- 以下の規格への準拠を目的としたシステムに最適:
 - EN 300 328、EN 300 440 Cat.2 および 3
 - FCC CFR47 Part 15
 - ARIB STD-T66

MCU 周辺機器

- ほとんどのデジタル ペリフェラルを任意の GPIO に配 線可能
- 4 つの 32 ビットまたは 8 つの 16 ビット汎用タイマ
- 12 ビット SAR ADC、200ksps、8 チャネル
- 8 ビット DAC
- 2 つのコンパレータ
- プログラマブル電流ソース
- 4つの UART、4つの SPI、2つの I²C、1つの I²S
- リアルタイム クロック (RTC)
- 温度およびバッテリモニタを内蔵

セキュリティイネーブラ (実現機能)

- セキュアブートのサポート
- セキュアキーストレージとデバイス ID をサポート
- 信頼できる実行環境に対応する Arm® TrustZone®
- AES 128 および 256 ビット暗号化アクセラレータ
- 公開鍵アクセラレータ
- SHA2 アクセラレータ (SHA-512 までのフル スイート)
- 真性乱数生成器 (TRNG)
- セキュア デバッグ ロック
- ソフトウェア アンチロールバック保護

開発ツールとソフトウェア

- 2.4GHz でのデュアルバンドおよび +10dBm 出力電 カ用の LP-EM-CC1354P10-6
- LP-XDS110、LP-XDS110ET または TMDSEMU110-U (TMDSEMU110-ETH アドオン使用) デバッグ プロ
- SimpleLink™ LOWPOWER F2 ソフトウェア開発キッ ト(SDK)
- SmartRF™ Studio による簡素な無線構成
- Sensor Controller Studio により低消費電力のセンシ ング アプリケーションを構築
- SysConfig システム コンフィギュレーション ツール

動作範囲

- オンチップの降圧型 DC/DC コンバータ
- 1.8V~3.8V のシングル電源電圧
- -40°C~+105°C



パッケージ

- 7mm × 7mm RGZ VQFN48 (GPIO 31 本)
- 8mm × 8mm RSK VQFN64 (GPIO 42 本)
- RoHS 準拠のパッケージ

2 アプリケーション

- 2400MHz~2480MHz の ISM および SRD システム 1
 - (最小 4kHz の受信帯域幅)
- ビルオートメーション
 - ビルディングのセキュリティシステム モーション検 出器、電子スマートロック、ドアおよび窓センサ、ガ レージドアシステム、ゲートウェイ
 - HVAC サーモスタット、ワイヤレス環境センサ、 HVAC システム コントローラ、ゲートウェイ
 - 防火システム 煙および熱感知器、火災警報制御パネル (FACP)
 - ビデオ監視 IP ネットワーク カメラ
 - エレベータとエスカレータ エレベータとエスカレータのエレベータメイン制御パネル
- 産業用輸送 アセットトラッキング
- ファクトリオートメーション/制御

• 医療用

- パーソナルケアとフィットネス
- 患者モニタと診断 医療用センサ パッチ、マルチ パラメータ メディカル モニタ
- 医療用機器
- 家庭用ヘルスケア 血糖値計、パルス オキシメータ
- 電子 POS (EPOS) 電子棚札 (ESL)
- 通信機器
 - 有線ネットワーク 無線 LAN または Wi-Fi アクセスポイント、エッジ ルータ
- パーソナル エレクトロニクス
 - ポータブル電子機器 RF スマート遠隔制御
 - ホーム シアターおよびエンターテインメント スマート スピーカ、スマート ディスプレイ、セット トップボックス
 - ネットワーク接続の周辺機器 民生用ワイヤレス モジュール、ポインティング デバイス、キーボードと キーパッド
 - ゲーム 電子玩具とロボット玩具
 - ウェアラブル (医療以外) スマートトラッカー、スマート衣料

3 概要

SimpleLink™ CC2674R10 デバイスはマルチプロトコルおよびマルチバンド 2.4GHz ワイヤレス マイコン (MCU) です。本デバイスは Thread、Zigbee、Bluetooth® 5.3 Low Energy、IEEE 802.15.4、IPv6 対応スマート オブジェクト (6LoWPAN)、テキサス・インスツルメンツ 15.4 スタック (2.4GHz) など各種独自システム、DMM (ダイナミック マルチプロトコル マネージャ)ドライバを使った同時マルチプロトコルをサポートしています。このデバイスは、ビルディングのセキュリティシステム、HVAC、医療、有線ネットワーク、携帯型電子機器、ホーム シアター & エンターテインメント市場の低消費電力の無線通信および高度なセンシングに最適化されています。このデバイスの主な特長を以下に示します。

- Arm® TrustZone® ベースのセキュアキーストレージ、デバイスID、トラステッド機能をサポート。
- SimpleLink LOWPOWER F2 ソフトウェア開発キット (SDK) で幅広いプロトコル スタックを柔軟にサポート。
- 0.92 µA の小さいスタンバイ電流 (全 256 kB SRAM 保持) によるバッテリ寿命が長いワイヤレス アプリケーション。
- 潜在的な放射線イベントによるデータの破損を防止する常時オン SRAM パリティによる、産業用市場向けの中断のない長い動作寿命のための小さい SER (ソフトエラーレート) FIT (Failure-in-time、故障率)。
- 柔軟性の高い低消費電力 RF トランシーバ機能を備えた専用のソフトウェア制御無線コントローラ (Arm® Cortex®-M0) により、複数の物理層および RF 規格をサポート。
- Bluetooth® Low Energy (125kbps の LE Coded PHY で -105dBm) に対応する優れた無線感度および堅牢 (選択 度、ブロッキング) 性能。

この CC2674R10 デバイスは、SimpleLink™ MCU プラットフォームの一部です。本プラットフォームは、単一のコア SDK (ソフトウェア開発キット) と豊富なツール セットを備えた使いやすい共通の開発環境を共有する Wi-Fi®、Bluetooth® Low Energy、Thread、Zigbee®、Sub-1GHz MCU、およびホスト MCU で構成されています。 SimpleLink™ プラットフォーム の統合を 1 回行うだけで、どのようなデバイスの組み合わせでも、ポートフォリオから自分の設計に追加でき、設計の要件 が変化した場合でも、コードを 100% 再利用することができます。 詳細については、 SimpleLink マイコン プラットフォーム をご覧ください。

Product Folder Links: CC2674R10

¹ サポートしているプロトコル規格、変調フォーマット、データレートの詳細については、RFコアを参照してください。



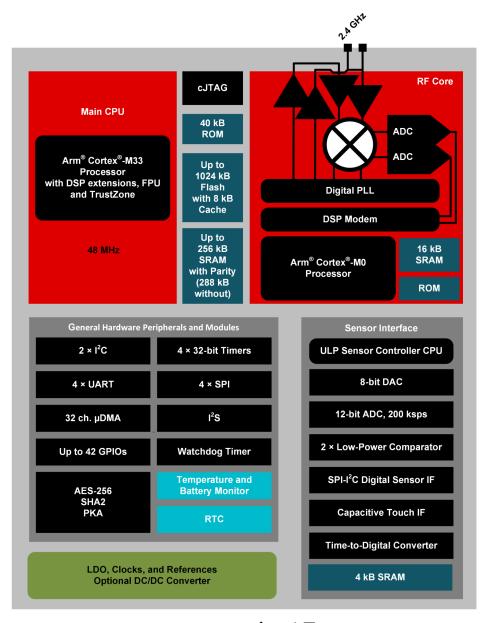
ソフトウェアの互換性に加えて、マルチバンド ワイヤレス MCU は 7mm × 7mm の QFN パッケージに封止済みで、352kB のフラッシュから 1MB のフラッシュまでのピン互換性があるので、設計のスケーラビリティを最大限に高めることができます。 テキサス・インスツルメンツの 2.4GHz デバイスの詳細については、www.ti.com/bluetooth をご覧ください。

製品情報

部品番号	パッケージ ⁽¹⁾	パッケージ サイズ
CC2674R106T0RGZ	VQFN (48)	7.00mm × 7.00mm
CC2674R106T0RSK	VQFN (64)	8.00mm × 8.00mm

(1) 詳細については、「メカニカル、パッケージ、および注文情報」を参照してください。

4機能ブロック図



CC2674R10 ブロック図



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5 Device Comparison

				F	RADIO	SUP	POR1	Г								PA	CKA	GE S	IZE	
Device	Sub-1GHz Prop.	2.4GHz Prop.	Wireless M-Bus	mioty	Wi-SUN®	Sidewalk	Bluetooth® LE	Zigbee	Thread	Multiprotocol	+20dBm PA	FLASH (kB)	RAM + Cache (kB)	GPIO	4 × 4 mm VQFN (24)	4 × 4 mm VQFN (32)	5 × 5 mm VQFN (32)	5 × 5 mm VQFN (40)	7 × 7 mm VQFN (48)	8 × 8 mm VQFN (64)
CC1310	1		√	1								32-128	16-20 + 8	10-30		√	V		√	
CC1311R3	√		√	1								352	32 + 8	22-30				1	√	
CC1311P3	√		√	1							√	352	32 + 8	26					√	
CC1312R	√		√	1	√							352	80 + 8	30					√	
CC1312R7	√		√	1	√	V				√		704	144 + 8	30					√	
CC1314R10	√		√	√	√	√				√		1024	256 + 8	30-46					√	√
CC1352R	V	√	√	√	√		√	√	1	√		352	80 + 8	28					√	
CC1354R10	√	√	√	V	√		√	√	√	√		1024	256 + 8	28-42					√	√
CC1352P	√	√	√	V	√		√	√	V	√	√	352	80 + 8	26					√	
CC1352P7	√	√	√	1	√	V	√	√	V	V	√	704	144 + 8	26					√	
CC1354P10	√	√	√	√	√	V	√	√	V	V	√	1024	256 + 8	26-42					√	√
CC2340R2 (1)		√					√	√				256	28	12	√					
CC2340R5 (2)		√					√	√	√			512	36	12-26	√			√		
CC2340R5-Q1							√					512	36	19			√			
CC2640R2F							√					128	20 + 8	10-31		√	√		√	
CC2642R							√					352	80 + 8	31					√	
CC2642R-Q1							√					352	80 + 8	31					√	
CC2651R3		√					√	√				352	32 + 8	23-31				√	√	
CC2651P3		√					√	√			√	352	32 + 8	22-26				√	√	
CC2652R		√					√	√	1	V		352	80 + 8	31					√	
CC2652RB		√					√	√	V	√		352	80 + 8	31					√	
CC2652R7		√					√	√	V	√		704	144 + 8	31					√	
CC2652P		√					√	√	√	√	1	352	80 + 8	26					√	
CC2652P7		√					√	√	V	√	1	704	144 + 8	26					√	
CC2674R10		√					√	√	V	√		1024	256 + 8	31-45					√	√
CC2674P10		√					√	√	√	√	V	1024	256 + 8	26-45					√	√

Zigbee and Proprietary RF support enabled by a future software update Zigbee and Thread support enabled by a future software update



6 Pin Configuration and Functions

6.1 Pin Diagram—RGZ Package (Top View)

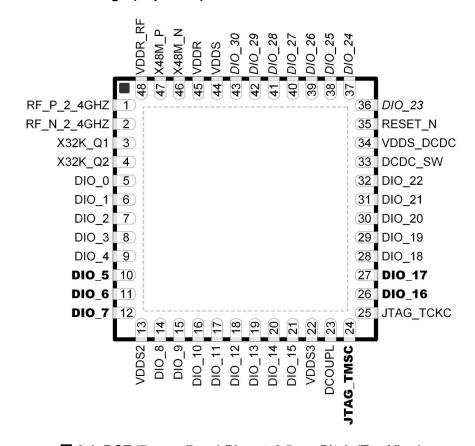


図 6-1. RGZ (7mm × 7mm) Pinout, 0.5mm Pitch (Top View)

The following I/O pins marked in ⊠ 6-1 in **bold** have high-drive capabilities:

- Pin 10, DIO_5
- Pin 11, DIO 6
- Pin 12, DIO 7
- Pin 24, JTAG_TMSC
- Pin 26, DIO_16
- Pin 27, DIO_17

The following I/O pins marked in \boxtimes 6-1 in *italics* have analog capabilities:

- Pin 36, DIO 23
- Pin 37, DIO_24
- Pin 38, DIO_25
- Pin 39, DIO_26
- Pin 40, DIO_27
- Pin 41, DIO_28
- Pin 42, DIO_29
- Pin 43, DIO_30



6.2 Signal Descriptions—RGZ Package

表 6-1. Signal Descriptions—RGZ Package

PIN				HIGH FACKAGE
NAME	NO.	I/O	TYPE	DESCRIPTION
DCDC_SW	33	_	Power	Output from internal DC/DC converter ⁽¹⁾
DCOUPL	23	_	Power	For decoupling of internal 1.27V regulated digital-supply (2)
DIO_0	5	I/O	Digital	GPIO
DIO_1	6	I/O	Digital	GPIO
DIO_2	7	I/O	Digital	GPIO
DIO_5	10	I/O	Digital	GPIO, high-drive capability
DIO_6	11	I/O	Digital	GPIO, high-drive capability
DIO_7	12	I/O	Digital	GPIO, high-drive capability
DIO_8	14	I/O	Digital	GPIO
DIO_9	15	I/O	Digital	GPIO
DIO_10	16	I/O	Digital	GPIO
DIO_11	17	I/O	Digital	GPIO
DIO_12	18	I/O	Digital	GPIO
DIO_13	19	I/O	Digital	GPIO
DIO_14	20	I/O	Digital	GPIO
DIO_15	21	I/O	Digital	GPIO
DIO_16	26	I/O	Digital	GPIO, JTAG_TDO, high-drive capability
DIO_17	27	I/O	Digital	GPIO, JTAG_TDI, high-drive capability
DIO_18	28	I/O	Digital	GPIO
DIO_19	29	I/O	Digital	GPIO
DIO_20	30	I/O	Digital	GPIO
DIO_21	31	I/O	Digital	GPIO
DIO_22	32	I/O	Digital	GPIO
DIO_23	36	I/O	Digital or Analog	GPIO, analog capability
DIO_24	37	I/O	Digital or Analog	GPIO, analog capability
DIO_25	38	I/O	Digital or Analog	GPIO, analog capability
DIO_26	39	I/O	Digital or Analog	GPIO, analog capability
DIO_27	40	I/O	Digital or Analog	GPIO, analog capability
DIO_28	41	I/O	Digital or Analog	GPIO, analog capability
DIO_29	42	I/O	Digital or Analog	GPIO, analog capability
DIO_30	43	I/O	Digital or Analog	GPIO, analog capability
EGP	_	_	GND	Ground—exposed ground pad ⁽³⁾
JTAG_TMSC	24	I/O	Digital	JTAG TMSC, high-drive capability
JTAG_TCKC	25	I	Digital	JTAG TCKC
RESET_N	35	L	Digital	Reset, active low. No internal pullup resistor
RF_P_2_4GHZ	1	_	RF	Positive 2.4GHz RF input signal to LNA during RX Positive 2.4GHz RF output signal from PA during TX
RF_N_2_4GHZ	2	_	RF	Negative 2.4GHz RF input signal to LNA during RX Negative 2.4GHz RF output signal from PA during TX
VDDR	45	_	Power	Internal supply, must be powered from the internal DC/DC converter or the internal LDO ⁽²⁾ (4) (6)
VDDR_RF	48	_	Power	Internal supply, must be powered from the internal DC/DC converter or the internal LDO ⁽²⁾ (5) (6)



表 6-1. Signal Descriptions—RGZ Package (続き)

PIN		I/O	TYPE	DESCRIPTION
NAME	NO.	"0	IIFE	DESCRIPTION
VDDS	44	_	Power	1.8V to 3.8V main chip supply ⁽¹⁾
VDDS2	13	_	Power	1.8V to 3.8V DIO supply ⁽¹⁾
VDDS3	22	_	Power	1.8V to 3.8V DIO supply ⁽¹⁾
VDDS_DCDC	34	_	Power	1.8V to 3.8V DC/DC converter supply
X48M_N	46	_	Analog	48MHz crystal oscillator pin N
X48M_P	47	_	Analog	48MHz crystal oscillator pin P
X32K_Q1	3	_	Analog	32kHz crystal oscillator pin 1
X32K_Q2	4	_	Analog	32kHz crystal oscillator pin 2

- (1) For more details, see the technical reference manual listed in セクション 10.2.
- (2) Do not supply external circuitry from this pin.
- (3) EGP is the only ground connection for the device. A good electrical connection to the device ground on a printed circuit board (PCB) is imperative for proper device operation.
- (4) If an internal DC/DC converter is not used, this pin is supplied internally from the main LDO.
- 5) If an internal DC/DC converter is not used, this pin must be connected to VDDR for supply from the main LDO.
- (6) Output from internal DC/DC and LDO is trimmed to 1.68V.

6.3 Connections for Unused Pins and Modules—RGZ Package

表 6-2. Connections for Unused Pins—RGZ Package

2 0 2. Commodicine for Gridoux 1 mo 1 (O2) working									
FUNCTION	SIGNAL NAME	PIN NUMBER	ACCEPTABLE PRACTICE(1)	PREFERRED PRACTICE ⁽¹⁾					
GPIO	DIO_n	5–12 14–21 26–32 36–43	NC or GND	NC					
32.768 kHz crystal	X32K_Q1	3	NC or GND	NC					
32.700 Ki iz Ciystai	X32K_Q2	4	INC OF GIND	INC					
DC/DC converter ⁽²⁾	DCDC_SW	33	NC	NC					
DO/DO CONVENIENCE	VDDS_DCDC	34	VDDS	VDDS					

- (1) NC = No connect
- When the DC/DC converter is not used, the inductor between DCDC_SW and VDDR can be removed. VDDR and VDDR_RF must still be connected and the 22µF DCDC capacitor must be kept on the VDDR net.

Product Folder Links: CC2674R10

資料に関するフィードバック(ご意見やお問い合わせ)を送信

6.4 Pin Diagram—RSK Package (Top View)

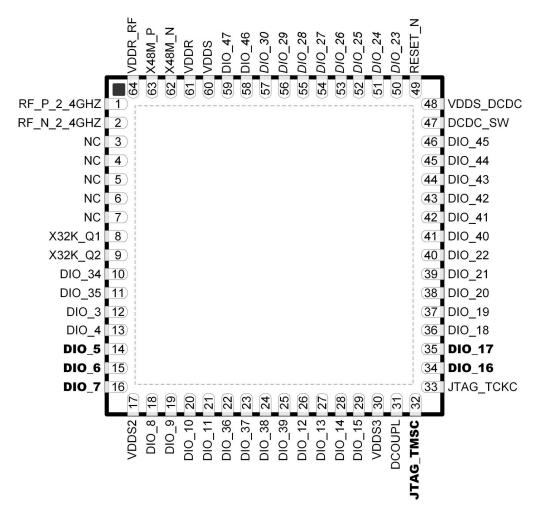


図 6-2. RSK (8mm × 8mm) Pinout, 0.4mm Pitch (Top View)

The following I/O pins marked in ⊠ 6-2 in **bold** have high-drive capabilities:

- Pin 14, DIO 5
- Pin 15, DIO 6
- Pin 16, DIO 7
- Pin 32, JTAG TMSC
- Pin 34, DIO_16
- Pin 35, DIO 17

The following I/O pins marked in \boxtimes 6-2 in *italics* have analog capabilities:

- Pin 50, DIO 23
- Pin 51, DIO_24
- Pin 52, DIO 25
- Pin 53, DIO_26
- Pin 54, DIO_27
- Pin 55, DIO 28
- Pin 56, DIO_29
- Pin 57, DIO_30



6.5 Signal Descriptions—RSK Package

表 6-3. Signal Descriptions—RSK Package

表 6-3. Signal Descriptions—RSK Package									
NAME NO.		1/0	TYPE	DESCRIPTION					
DCDC_SW	47	_	Power	Output from internal DC/DC converter ⁽¹⁾					
DCOUPL	31	_	Power	For decoupling of internal 1.27V regulated digital-supply (2)					
DIO_3	12	I/O	Digital	GPIO					
DIO_4	13	I/O	Digital	GPIO					
DIO_5	14	I/O	Digital	GPIO, high-drive capability					
DIO_6	15	I/O	Digital	GPIO, high-drive capability					
DIO_7	16	I/O	Digital	GPIO, high-drive capability					
DIO_8	18	I/O	Digital	GPIO					
DIO_9	19	I/O	Digital	GPIO					
DIO_10	20	I/O	Digital	GPIO					
DIO_11	21	I/O	Digital	GPIO					
DIO_12	26	I/O	Digital	GPIO					
DIO_12	27	I/O	Digital	GPIO					
DIO_14	28	I/O	Digital	GPIO					
DIO_15	29	I/O	Digital	GPIO					
DIO_16	34	I/O	Digital	GPIO, JTAG_TDO, high-drive capability					
DIO_17	35	I/O	Digital	GPIO, JTAG_TDI, high-drive capability					
DIO_18	36	I/O	Digital	GPIO					
DIO_19	37	I/O	Digital	GPIO					
DIO_20	38	I/O	Digital	GPIO					
DIO_21	39	I/O	Digital	GPIO					
DIO_22	40	I/O	Digital	GPIO					
DIO_23	50	I/O	Digital or Analog	GPIO, analog capability					
DIO_24	51	I/O	Digital or Analog	GPIO, analog capability					
DIO_25	52	I/O	Digital or Analog	GPIO, analog capability					
DIO_26	53	I/O	Digital or Analog	GPIO, analog capability					
DIO_27	54	I/O	Digital or Analog	GPIO, analog capability					
DIO_28	55	I/O	Digital or Analog	GPIO, analog capability					
DIO_29	56	I/O	Digital or Analog	GPIO, analog capability					
DIO_30	57	I/O	Digital	GPIO, analog capability					
DIO_34	10	I/O	Digital	GPIO					
 DIO_35	11	I/O	Digital	GPIO					
DIO_36	22	I/O	Digital	GPIO					
DIO_37	23	I/O	Digital	GPIO					
DIO_38	24	I/O	Digital	GPIO					
DIO_39	25	I/O	Digital	GPIO					
 DIO_40	41	I/O	Digital	GPIO					
DIO_41	42	I/O	Digital	GPIO					
DIO_42	43	I/O	Digital	GPIO					
DIO_43	44	I/O	Digital	GPIO					
DIO_44	45	I/O	Digital	GPIO					
	46								
DIO_45	46	I/O	Digital	GPI0					

表 6-3. Signal Descriptions—RSK Package (続き)

PIN				
NAME NO.		I/O	TYPE	DESCRIPTION
DIO 46	58	I/O	Digital	GPIO
DIO_47	59	I/O	Digital	GPIO
EGP			GND	Ground—exposed ground pad ⁽³⁾
JTAG TMSC	32	I/O	Digital	JTAG TMSC, high-drive capability
JTAG_TCKC	33	I/O	Digital	JTAG TOKC
		ı	Digital	
NC	3	_	_	No Connect
NC	4	_	_	No Connect
NC	5	_	_	No Connect
NC	6	_	_	No Connect
NC	7	_	_	No Connect
RESET_N	49	I	Digital	Reset, active low. No internal pullup resistor
RF_P_2_4GHZ	1	_	RF	Positive 2.4GHz RF input signal to LNA during RX Positive 2.4GHz RF output signal from PA during TX
RF_N_2_4GHZ	2	_	RF	Negative 2.4GHz RF input signal to LNA during RX Negative 2.4GHz RF output signal from PA during TX
VDDR	61	_	Power	Internal supply, must be powered from the internal DC/DC converter or the internal LDO ⁽²⁾ (4) (6)
VDDR_RF	64	_	Power	Internal supply, must be powered from the internal DC/DC converter or the internal LDO ⁽²⁾ (5) (6)
VDDS	60	_	Power	1.8V to 3.8V main chip supply ⁽¹⁾
VDDS2	17	_	Power	1.8V to 3.8V DIO supply ⁽¹⁾
VDDS3	30	_	Power	1.8V to 3.8V DIO supply ⁽¹⁾
VDDS_DCDC	48	_	Power	1.8V to 3.8V DC/DC converter supply
X48M_N	62	_	Analog	48MHz crystal oscillator pin N
X48M_P	63	_	Analog	48MHz crystal oscillator pin P
X32K_Q1	8	_	Analog	32kHz crystal oscillator pin 1
X32K_Q2	9	_	Analog	32kHz crystal oscillator pin 2

- (1) For more details, see technical reference manual listed in the documentation support section.
- (2) Do not supply external circuitry from this pin.
- (3) EGP is the only ground connection for the device. Good electrical connection to device ground on printed circuit board (PCB) is imperative for proper device operation.
- (4) If internal DC/DC converter is not used, this pin is supplied internally from the main LDO.
- (5) If internal DC/DC converter is not used, this pin must be connected to VDDR for supply from the main LDO.
- (6) Output from internal DC/DC and LDO is trimmed to 1.68V.



6.6 Connection of Unused Pins and Module—RSK Package

表 6-4. Connections for Unused Pins—RSK Package

FUNCTION	SIGNAL NAME	PIN NUMBER	ACCEPTABLE PRACTICE(1)	PREFERRED PRACTICE(1)	
GPIO	DIO_n	10–16 14–21 26–32 36–43	NC or GND	NC	
20.70011	X32K_Q1	8	NC or GND	NC	
32.768kHz crystal	X32K_Q2	9	INC OF GIND	NC	
No Connects	NC	3–7	NC	NC	
DC/DC converter ⁽²⁾	DCDC_SW	47	NC	NC	
DC/DC converter	VDDS_DCDC	48	VDDS	VDDS	

⁽¹⁾ NC = No connect

⁽²⁾ When the DC/DC converter is not used, the inductor between DCDC_SW and VDDR can be removed. VDDR and VDDR_RF must still be connected and the 22µF DCDC capacitor must be kept on the VDDR net.

7 Specifications

7.1 Absolute Maximum Ratings

Over operating free-air temperature range (unless otherwise noted)(1) (2)

			MIN	MAX	UNIT
VDDS(3)	Supply voltage		-0.3	4.1	V
	Voltage on any digital pin	(4) (5)	-0.3	VDDS + 0.3, max 4.1	V
	Voltage on crystal oscilla	tor pins, X32K_Q1, X32K_Q2, X48M_N and X48M_P	-0.3	VDDR + 0.3, max 2.25	V
		Voltage scaling enabled	-0.3	VDDS	
V _{in}	Voltage on ADC input	Voltage scaling disabled, internal reference	-0.3	1.49	V
		Voltage scaling disabled, VDDS as reference		VDDS / 2.9	
T _{stg}	Storage temperature		-40	150	°C

- Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute Maximum Ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime.
- (2) All voltage values are with respect to ground, unless otherwise noted.
- (3) VDDS_DCDC, VDDS2, and VDDS3 must be at the same potential as VDDS.
- (4) Including analog capable DIOs.
- (5) Injection current is not supported on any GPIO pin.

7.2 ESD Ratings

				VALUE	UNIT
V	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	All pins	±2000	V
V _{ESD}	Liectiostatic discharge	Charged device model (CDM), per ANSI/ESDA/JEDEC JS-002 ⁽²⁾	All pins	±500	V

- (1) JEDEC document JEP155 states that 500V HBM allows safe manufacturing with a standard ESD control process
- (2) JEDEC document JEP157 states that 250V CDM allows safe manufacturing with a standard ESD control process

7.3 Recommended Operating Conditions

Over operating free-air temperature range (unless otherwise noted)

	MIN	MAX	UNIT
Operating ambient temperature ⁽¹⁾	-40	105	°C
Operating supply voltage (VDDS)	1.8	3.8	V
Rising supply voltage slew rate	0	100	mV/μs
Falling supply voltage slew rate ⁽²⁾	0	20	mV/μs

- Operation at or near maximum operating temperature for extended durations will result in lifetime reduction.
- (2) For small coin-cell batteries, with high worst-case end-of-life equivalent source resistance, a 22 μF VDDS input capacitor must be used to ensure compliance with this slew rate.

7.4 Power Supply and Modules

Over operating free-air temperature range (unless otherwise noted).

<u> </u>					
PARAMETER		MIN TYP	MAX	UNIT	
VDDS Power-on-Reset (POR) threshold		1.1 - 1.55		V	
VDDS Brown-out Detector (BOD) (1)	Rising threshold	1.77		V	
VDDS Brown-out Detector (BOD), before initial boot (2)	Rising threshold	1.70		V	
VDDS Brown-out Detector (BOD) (1)	Falling threshold	1.75		V	

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- 1) For boost mode (VDDR =1.95 V), TI drivers software initialization will trim VDDS BOD limits to maximum (approximately 2.0 V).
- (2) Brown-out Detector is trimmed at initial boot, value is kept until device is reset by a POR reset or the RESET_N pin.

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7.5 Power Consumption - Power Modes

When measured on the $T_c = 25^{\circ}C$, $V_{DDS} = 3.0V$ with DC/DC enabled unless otherwise noted.

	PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
Core Curr	ent Consumption				
	Reset and Shutdown	Reset. RESET_N pin asserted or VDDS below power-on-reset threshold	150		nA
	Siluldowii	Shutdown. No clocks running, no retention	128.6		nA
		RTC running, CPU, 256kB RAM and (partial) register retention. RCOSC_LF	1.06		μA
	Standby without cache	RTC running, CPU, 128kB RAM and (partial) register retention. RCOSC_LF	0.96		μA
	retention	RTC running, CPU, 256kB RAM and (partial) register retention XOSC_LF	1.19		μA
		RTC running, CPU, 128kB RAM and (partial) register retention XOSC_LF	1.09		μΑ
I _{core}		RTC running, CPU, 256kB RAM and (partial) register retention. RCOSC_LF	2.55		μA
	Standby	RTC running, CPU, 128kB RAM and (partial) register retention. RCOSC_LF	2.45		μA
	with cache retention	RTC running, CPU, 256kB RAM and (partial) register retention. XOSC_LF	2.66		μΑ
		RTC running, CPU, 128kB RAM and (partial) register retention. XOSC_LF	2.57		μΑ
	Idle	Supply Systems and RAM powered RCOSC_HF	720.9		μA
	Active	MCU running CoreMark at 48MHz with parity enabled RCOSC_HF	4.13		mA
	Active	MCU running CoreMark at 48MHz with parity disabled RCOSC_HF	3.97		mA
Periphera	l Current Consumption				
	Peripheral power domain	Delta current with domain enabled	74.0		
	Serial power domain	Delta current with domain enabled	6.89		
	RF Core	Delta current with power domain enabled, clock enabled, RF core idle	120.4		
	μDMA	Delta current with clock enabled, module is idle	68.2		
	Timers	Delta current with clock enabled, module is idle ⁽¹⁾	115.4		
I _{peri}	I2C	Delta current with clock enabled, module is idle	11.5		μΑ
	128	Delta current with clock enabled, module is idle	26.1		
	SPI	Delta current with clock enabled, module is idle ⁽²⁾	65.9		
	UART	Delta current with clock enabled, module is idle ⁽³⁾	135.1		
	CRYPTO (AES)	Delta current with clock enabled, module is idle	18.6		
	PKA	Delta current with clock enabled, module is idle	79.3		
	TRNG	Delta current with clock enabled, module is idle	24.69		
Sensor Co	ontroller Engine Consump	tion			
	Active mode	24MHz, infinite loop	849		
I _{SCE}	Low-power mode	2MHz, infinite loop	32		μA

- Only one GPTimer running Only one SPI running Only one UART running (1)
- (2)

7.6 Power Consumption - Radio Modes

When measured on the reference design with $T_c = 25^{\circ}C$, $V_{DDS} = 3.0V$ with DC/DC enabled unless otherwise noted.

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
I_radio	Radio receive current, 2.44GHz (BLE)	2440MHz		6.4		mA
I_radio Radio transmit current 2.4GHz PA (BLE)	0dBm output power setting 2440MHz		7.3		mA	
	+5dBm output power setting 2440MHz		9.8		mA	

7.7 Nonvolatile (Flash) Memory Characteristics

Over operating free-air temperature range and V_{DDS} = 3.0V (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Flash sector size			2		kB
Supported flash erase cycles before failure, full bank ⁽¹⁾ (2)		30			k Cycles
Supported flash erase cycles before failure, single sector ⁽³⁾		60			k Cycles
Maximum number of write operations per row before sector erase ⁽⁴⁾				83	Write Operations
Flash retention	105 °C Tj	11.4			Years
Flash sector erase current	Average delta current		1.0		mA
Flash sector erase time ⁽⁵⁾	Zero cycles		10		ms
	30k cycles			4000	ms

- (1) A full bank erase is counted as a single erase cycle on each sector.
- (2) Aborting flash during erase or program modes is not a safe operation.
- (3) Up to 4 customer-designated sectors can be individually erased an additional 30k times beyond the baseline bank limitation of 30k cycles.
- (4) Éach wordline is 2048 bits (or 256 bytes) wide. This limitation corresponds to sequential memory writes of 4 (3.1) bytes minimum per write over a whole wordline. If additional writes to the same wordline are required, a sector erase is required once the maximum number of write operations per row is reached.
- (5) This number is dependent on Flash aging and increases over time and erase cycles.

7.8 Thermal Resistance Characteristics

		PAC		
	THERMAL METRIC(1)	RGZ (VQFN)	RSK (VQFN)	UNIT
		48 PINS	64 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	23.4	25.1	°C/W ⁽²⁾
R _{0JC(top)}	Junction-to-case (top) thermal resistance	13.3	11.5	°C/W ⁽²⁾
$R_{\theta JB}$	Junction-to-board thermal resistance	8.0	8.9	°C/W ⁽²⁾
ΨЈТ	Junction-to-top characterization parameter	0.1	0.1	°C/W ⁽²⁾
ΨЈВ	Junction-to-board characterization parameter	7.9	8.8	°C/W ⁽²⁾
R _{0JC(bot)}	Junction-to-case (bottom) thermal resistance	1.7	1.2	°C/W ⁽²⁾

⁽¹⁾ For more information about traditional and new thermal metrics, see Semiconductor and IC Package Thermal Metrics.

7.9 RF Frequency Bands

Over operating free-air temperature range (unless otherwise noted).

PARAMETER	MIN	TYP MAX	UNIT
Frequency bands	2360	2500	MHz

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^{(2) °}C/W = degrees Celsius per watt.



7.10 Bluetooth Low Energy—Receive (RX)

When measured on the LP-EM-CC1354P10-1 reference design with T_c = 25°C, V_{DDS} = 3.0V, f_{RF} = 2440MHz with DC/DC enabled unless otherwise noted. All measurements are performed at the antenna input with a combined RX and TX path. All measurements are performed conducted.

Receiver sensitivity	PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
Receiver saturation	125kbps (LE Coded)				
Difference between the incoming carrier frequency and the internally generated carrier frequency	Receiver sensitivity	Differential mode. BER = 10 ⁻³	-105		dBm
Data rate error tolerance Difference between incoming data rate and the internally generated data rate (37-9)/ep packets) Data rate error tolerance Difference between incoming data rate and the internally generated data rate (37-9)/ep packets) Difference between incoming data rate and the internally generated data rate (37-9)/ep packets) Difference between incoming data rate and the internally generated data rate (37-9)/ep packets) Difference between incoming data rate and the internally generated data rate (38-9)/ep packets) Varieted signal at -7968m, modulated interferer in channel, BER = 10-3 Selectivity, ±1MHz(!)	Receiver saturation	Differential mode. BER = 10 ⁻³	>5		dBm
Data rate error tolerance Difference between incoming data rate and the internally generated data rate (37-byte packets) Difference between incoming data rate and the internally generated data rate (256-byte packets) Co-channel rejection¹¹ Wanted signal at -794Bm, modulated interferer in channel, BER = 10⁻3 dB Selectivity, ±1MHz(¹) ±1MHz BER = 10⁻3 dB Wanted signal at -794Bm, modulated interferer at ±1MHz, BER = 10⁻3 dB Selectivity, ±2MHz(¹) ±2MHz BER = 10⁻3 dB Wanted signal at -794Bm, modulated interferer at ±2MHz, BER = 10⁻3 dB Selectivity, ±3MHz(¹) ±2MHz, BER = 10⁻3 dB Selectivity, ±3MHz(¹) Wanted signal at -794Bm, modulated interferer at ±3MHz, BER = 10⁻3 dB Selectivity, ±3MHz(¹) Wanted signal at -794Bm, modulated interferer at ±4MHz, BER = 10⁻3 dB Selectivity, ±4MHz(¹) Wanted signal at -794Bm, modulated interferer at ±4MHz, BER = 10⁻3 dB Selectivity, ±5MHz(¹) Wanted signal at -794Bm, modulated interferer at ±5MHz, BER = 10⁻3 dB Selectivity, ±5MHz(²) Wanted signal at -794Bm, modulated interferer at ±5MHz, BER = 10⁻3 dB Selectivity, ±5MHz(²) Wanted signal at -794Bm, modulated interferer at ±5MHz, BER = 10⁻3 dB Selectivity, Image frequency Wanted signal at -794Bm, modulated interferer at 1 dB Selectivity, Image frequency Wanted signal at -794Bm, modulated interferer at 1 dB Selectivity, Image frequency Wanted signal at -794Bm, modulated interferer at 1 dB Selectivity, Image frequency Wanted signal at -794Bm, modulated interferer at 1 dB Selectivity, Image frequency Manted signal at -794Bm, modulated interferer at 1 dB Selectivity, ±5MHz(²) dB dB Selectivity, ±5MHz(²) dB dB Selectivity, ±5MHz(²) dB dB dB Selectivity, ±5MHz(²) dB dB dB Selectivity, ±5MHz(²) dB dB dB dB dB dB dB d	Frequency error tolerance		> (-300 / 300)		kHz
Co-channel rejection(¹) Wanted signal at -796Bm, modulated interferer at 1.5 4.5	Data rate error tolerance	, ,	> (-320 / 240)		ppm
Carchannet rejection Carchannet EBER = 10-3 Carchannet	Data rate error tolerance		> (-100 / 125)		ppm
Selectivity, ±1MHz ⁽¹⁾	Co-channel rejection ⁽¹⁾		-1.5		dB
25 25 25 25 25 25 25 25	Selectivity, ±1MHz ⁽¹⁾		8 / 4.5 ⁽²⁾		dB
Selectivity, ±3MHz 2:07 43/43-07 43 43 43 43 43 43 43 4	Selectivity, ±2MHz ⁽¹⁾		44 / 39 ⁽²⁾		dB
### Selectivity, ±3MM+Z ⁻¹ ### ### ### ### ### ### ### ### ### #	Selectivity, ±3MHz ⁽¹⁾		43 / 43 ⁽²⁾		dB
### ### ### ### ### ### ### ### ### ##	Selectivity, ±4MHz ⁽¹⁾		44 / 43 ⁽²⁾		dB
### ### #### ########################	Selectivity, ±6MHz ⁽¹⁾	Wanted signal at –79dBm, modulated interferer at ≥ ±6MHz, BER = 10 ⁻³	48 / 43 ⁽²⁾		dB
Selectivity, Image frequency Ifrequency Fequency	Selectivity, ±7MHz		51 / 45 ⁽²⁾		dB
1MHz. Wanted signal at ¬79dBm, modulated interferer at ±1MHz(1) ±1MHz(1) ±1MHz(1) ±1MHz from image frequency, BER = 10 ⁻³ 89 dB RSSI Accuracy (+/-) ±4 dB 500kbps (LE Coded) ±4 dB 500kbps (LE Coded) 500kbps (LE	Selectivity, Image frequency ⁽¹⁾		39		dB
### A	Selectivity, Image frequency ±1MHz ⁽¹⁾	1MHz. Wanted signal at –79dBm, modulated interferer at	4.5 / 44 ⁽²⁾		dB
Solve to the content of the content	RSSI Range		89		dB
Receiver sensitivity Differential mode. BER = 10 ⁻³ Receiver saturation Differential mode. BER = 10 ⁻³ Differential mode. BER = 10 ⁻³ Prequency error tolerance Difference between the incoming carrier frequency and the internally generated carrier frequency Data rate error tolerance Difference between incoming data rate and the internally generated data rate (37-byte packets) Data rate error tolerance Difference between incoming data rate and the internally generated data rate (27-byte packets) Difference between incoming data rate and the internally generated data rate (255-byte packets) Data rate error tolerance Difference between incoming data rate and the internally generated data rate (255-byte packets) Co-channel rejection(1) Wanted signal at −72dBm, modulated interferer in channel, BER = 10 ⁻³ Selectivity, ±1MHz(1) Wanted signal at −72dBm, modulated interferer at ±1MHz, BER = 10 ⁻³ Selectivity, ±2MHz(1) Wanted signal at −72dBm, modulated interferer at ±2MHz, BER = 10 ⁻³ Selectivity, ±3MHz(1) Wanted signal at −72dBm, modulated interferer at ±44 / 41(2) dB Selectivity, ±4MHz(1) Wanted signal at −72dBm, modulated interferer at ±44 / 43(2) dB Selectivity, ±4MHz(1) Wanted signal at −72dBm, modulated interferer at ±44 / 43(2) dB Selectivity, ±4MHz(1) Wanted signal at −72dBm, modulated interferer at ±46 / 43(2) Wanted signal at −72dBm, modulated interferer at ±66 / 43(2) Wanted signal at −72dBm, modulated interferer at ≥ ±66 / 43(2) Wanted signal at −72dBm, modulated interferer at ≥ ±66 / 43(2) Wanted signal at −72dBm, modulated interferer at ≥ ±66 / 43(2) Wanted signal at −72dBm, modulated interferer at ≥ ±66 / 43(2) Wanted signal at −72dBm, modulated interferer at ≥ ±66 / 43(2) Wanted signal at −72dBm, modulated interferer at ≥ ±66 / 43(2) Wanted signal at −72dBm, modulated interferer at ≥ ±66 / 43(2) Wanted signal at −72dBm, modulated interferer at ≥ ±66 / 43(2) Wanted signal at −72dBm, modulated interferer at ≥ ±66 / 43(2) Wanted signal at −72dBm, modulated int	RSSI Accuracy (+/-)		±4		dB
Receiver saturation Differential mode. BER = 10 ⁻³ > 5 dBm Frequency error tolerance Difference between the incoming carrier frequency and the internally generated carrier frequency Data rate error tolerance Difference between incoming data rate and the internally generated data rate (37-byte packets) Data rate error tolerance Difference between incoming data rate and the internally generated data rate (25-byte packets) Data rate error tolerance Difference between incoming data rate and the internally generated data rate (255-byte packets) Ppm Co-channel rejection(¹) Wanted signal at −72dBm, modulated interferer in channel, BER = 10 ⁻³ Selectivity, ±1MHz(¹) Wanted signal at −72dBm, modulated interferer at ±1MHz, BER = 10 ⁻³ Selectivity, ±2MHz(¹) Wanted signal at −72dBm, modulated interferer at ±2MHz, BER = 10 ⁻³ Selectivity, ±3MHz(¹) Wanted signal at −72dBm, modulated interferer at ±3MHz, BER = 10 ⁻³ Selectivity, ±4MHz(¹) Wanted signal at −72dBm, modulated interferer at ±4MHz, BER = 10 ⁻³ Selectivity, ±4MHz(¹) Wanted signal at −72dBm, modulated interferer at ±4MHz, BER = 10 ⁻³ Selectivity, ±4MHz(¹) Wanted signal at −72dBm, modulated interferer at ±4MHz, BER = 10 ⁻³ Wanted signal at −72dBm, modulated interferer at ±4MHz, BER = 10 ⁻³ Selectivity, ±6MHz(¹) Wanted signal at −72dBm, modulated interferer at ±6MHz, BER = 10 ⁻³ Wanted signal at −72dBm, modulated interferer at ±6MHz, BER = 10 ⁻³ Wanted signal at −72dBm, modulated interferer at ±6MHz, BER = 10 ⁻³ Wanted signal at −72dBm, modulated interferer at ≥ ±6MHz, BER = 10 ⁻³ Wanted signal at −72dBm, modulated interferer at ≥ ±6MHz, BER = 10 ⁻³	500kbps (LE Coded)				
Difference between the incoming carrier frequency and the internally generated carrier frequency Data rate error tolerance Difference between incoming data rate and the internally generated data rate (37-byte packets) Data rate error tolerance Difference between incoming data rate and the internally generated data rate (27-byte packets) Data rate error tolerance Difference between incoming data rate and the internally generated data rate (255-byte packets) Popm Co-channel rejection ⁽¹⁾ Wanted signal at -72dBm, modulated interferer in channel, BER = 10 ⁻³ Wanted signal at -72dBm, modulated interferer at ±1MHz, BER = 10 ⁻³ Selectivity, ±2MHz ⁽¹⁾ Wanted signal at -72dBm, modulated interferer at ±2MHz, BER = 10 ⁻³ Wanted signal at -72dBm, modulated interferer at ±3MHz, BER = 10 ⁻³ Selectivity, ±3MHz ⁽¹⁾ Wanted signal at -72dBm, modulated interferer at ±4MHz, BER = 10 ⁻³ Selectivity, ±4MHz ⁽¹⁾ Wanted signal at -72dBm, modulated interferer at ±4MHz, BER = 10 ⁻³ Selectivity, ±4MHz ⁽¹⁾ Wanted signal at -72dBm, modulated interferer at ±4MHz, BER = 10 ⁻³ Wanted signal at -72dBm, modulated interferer at ±4MHz, BER = 10 ⁻³ Selectivity, ±6MHz ⁽¹⁾ Wanted signal at -72dBm, modulated interferer at ±6MHz, BER = 10 ⁻³ Wanted signal at -72dBm, modulated interferer at ±6MHz, BER = 10 ⁻³ Wanted signal at -72dBm, modulated interferer at ≥ ±6MHz, BER = 10 ⁻³ Wanted signal at -72dBm, modulated interferer at ≥ ±6MHz, BER = 10 ⁻³	Receiver sensitivity	Differential mode. BER = 10 ⁻³	-100		dBm
the internally generated carrier frequency Data rate error tolerance Difference between incoming data rate and the internally generated data rate (37-byte packets) Data rate error tolerance Difference between incoming data rate and the internally generated data rate (255-byte packets) Data rate error tolerance Difference between incoming data rate and the internally generated data rate (255-byte packets) Co-channel rejection ⁽¹⁾ Wanted signal at -72dBm, modulated interferer in channel, BER = 10 ⁻³ Selectivity, ±1MHz ⁽¹⁾ Wanted signal at -72dBm, modulated interferer at ±1MHz, BER = 10 ⁻³ Selectivity, ±2MHz ⁽¹⁾ Wanted signal at -72dBm, modulated interferer at ±3MHz, BER = 10 ⁻³ Selectivity, ±3MHz ⁽¹⁾ Wanted signal at -72dBm, modulated interferer at ±3MHz, BER = 10 ⁻³ Wanted signal at -72dBm, modulated interferer at ±44 / 41 ⁽²⁾ dB Selectivity, ±4MHz ⁽¹⁾ Wanted signal at -72dBm, modulated interferer at ±4MHz, BER = 10 ⁻³ Wanted signal at -72dBm, modulated interferer at ±4MHz, BER = 10 ⁻³ Selectivity, ±6MHz ⁽¹⁾ Wanted signal at -72dBm, modulated interferer at ±6MHz, BER = 10 ⁻³ Wanted signal at -72dBm, modulated interferer at ≥ ±6MHz, BER = 10 ⁻³ Wanted signal at -72dBm, modulated interferer at ≥ ±6MHz, BER = 10 ⁻³ Wanted signal at -72dBm, modulated interferer at ≥ ±6MHz, BER = 10 ⁻³	Receiver saturation	Differential mode. BER = 10 ⁻³	> 5		dBm
Data rate error tolerance generated data rate (37-byte packets) Data rate error tolerance Difference between incoming data rate and the internally generated data rate (255-byte packets) Co-channel rejection ⁽¹⁾ Wanted signal at -72dBm, modulated interferer in channel, BER = 10 ⁻³ Selectivity, ±1MHz ⁽¹⁾ Wanted signal at -72dBm, modulated interferer at ±1MHz, BER = 10 ⁻³ Selectivity, ±2MHz ⁽¹⁾ Wanted signal at -72dBm, modulated interferer at ±2MHz, BER = 10 ⁻³ Selectivity, ±3MHz ⁽¹⁾ Wanted signal at -72dBm, modulated interferer at ±3MHz, BER = 10 ⁻³ Selectivity, ±3MHz ⁽¹⁾ Wanted signal at -72dBm, modulated interferer at ±3MHz, BER = 10 ⁻³ Selectivity, ±4MHz ⁽¹⁾ Wanted signal at -72dBm, modulated interferer at ±4MHz, BER = 10 ⁻³ Selectivity, ±6MHz ⁽¹⁾ Wanted signal at -72dBm, modulated interferer at ±4MHz, BER = 10 ⁻³ Wanted signal at -72dBm, modulated interferer at ±6MHz, BER = 10 ⁻³ Wanted signal at -72dBm, modulated interferer at ±6MHz, BER = 10 ⁻³ Wanted signal at -72dBm, modulated interferer at ≥4MHz, BER = 10 ⁻³ Wanted signal at -72dBm, modulated interferer at ≥4MHz, BER = 10 ⁻³ Wanted signal at -72dBm, modulated interferer at ≥4MHz, BER = 10 ⁻³ Wanted signal at -72dBm, modulated interferer at ≥4MHz, BER = 10 ⁻³	Frequency error tolerance	9 ' '	> (-300 / 300)		kHz
Data rate error tolerance generated data rate (255-byte packets) Co-channel rejection ⁽¹⁾ Wanted signal at -72dBm, modulated interferer in channel, BER = 10-3 Selectivity, ±1MHz ⁽¹⁾ Wanted signal at -72dBm, modulated interferer at ±1MHz, BER = 10-3 Wanted signal at -72dBm, modulated interferer at ±2MHz, BER = 10-3 Selectivity, ±2MHz ⁽¹⁾ Wanted signal at -72dBm, modulated interferer at ±3MHz, BER = 10-3 Selectivity, ±3MHz ⁽¹⁾ Wanted signal at -72dBm, modulated interferer at ±3MHz, BER = 10-3 Selectivity, ±4MHz ⁽¹⁾ Wanted signal at -72dBm, modulated interferer at ±44/43(2) dB Selectivity, ±6MHz ⁽¹⁾ Wanted signal at -72dBm, modulated interferer at ±6MHz, BER = 10-3 Wanted signal at -72dBm, modulated interferer at ≥ ±6MHz, BER = 10-3 Wanted signal at -72dBm, modulated interferer at ≥ ±6MHz, BER = 10-3 Wanted signal at -72dBm, modulated interferer at ≥ ±6MHz, BER = 10-3 Wanted signal at -72dBm, modulated interferer at ≥ ±6MHz, BER = 10-3	Data rate error tolerance		> (-450 / 450)		ppm
Co-channel rejection channel, BER = 10^{-3}	Data rate error tolerance		> (–175 / 175)		ppm
Selectivity, $\pm 1 \text{MHz}^{(1)}$ $\pm 1 \text{MHz}$, $\pm 1 \text{MHz}$	Co-channel rejection ⁽¹⁾		-3.5		dB
	Selectivity, ±1MHz ⁽¹⁾	±1MHz, BER = 10 ⁻³	8 / 4 ⁽²⁾		dB
	Selectivity, ±2MHz ⁽¹⁾		41 / 37 ⁽²⁾		dB
Selectivity, $\pm 4\text{MHz}$. $\pm 4\text{MHz}, \text{BER} = 10^{-3}$ Wanted signal at -72dBm , modulated interferer at \geq $\pm 6\text{MHz}, \text{BER} = 10^{-3}$ dB Wanted signal at -72dBm , modulated interferer at \geq $\pm 6\text{MHz}, \text{BER} = 10^{-3}$ Wanted signal at -72dBm , modulated interferer at \geq $40 / 45(2)$ dB	Selectivity, ±3MHz ⁽¹⁾		44 / 41 ⁽²⁾		dB
±6MHz, BER = 10 ⁻³ Wanted signal at −72dBm, modulated interferer at ≥ 46 / 43 ⁽²⁾ dB	Selectivity, ±4MHz ⁽¹⁾		44 / 43 ⁽²⁾		dB
	Selectivity, ±6MHz ⁽¹⁾		46 / 43 ⁽²⁾		dB
	Selectivity, ±7MHz		49 / 45 ⁽²⁾		dB

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7.10 Bluetooth Low Energy—Receive (RX) (続き)

When measured on the LP-EM-CC1354P10-1 reference design with T_c = 25°C, V_{DDS} = 3.0V, f_{RF} = 2440MHz with DC/DC enabled unless otherwise noted. All measurements are performed at the antenna input with a combined RX and TX path. All measurements are performed conducted.

PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
Selectivity, Image frequency ⁽¹⁾	Wanted signal at –72dBm, modulated interferer at image frequency, BER = 10 ⁻³	37		dB
Selectivity, Image frequency ±1MHz ⁽¹⁾	Note that Image frequency + 1MHz is the Co- channel – 1MHz. Wanted signal at –72dBm, modulated interferer at ±1MHz from image frequency, BER = 10 ⁻³	4 / 46 ⁽²⁾		dB
RSSI Range		85		dB
RSSI Accuracy (+/-)		±4		dB
1 Mbps (LE 1M)				
Receiver sensitivity	Differential mode. BER = 10 ⁻³	– 97		dBm
Receiver saturation	Differential mode. BER = 10 ⁻³	> 5		dBm
Frequency error tolerance	Difference between the incoming carrier frequency and the internally generated carrier frequency	> (-350 / 350)		kHz
Data rate error tolerance	Difference between incoming data rate and the internally generated data rate (37-byte packets)	> (-750 / 750)		ppm
Co-channel rejection ⁽¹⁾	Wanted signal at –67dBm, modulated interferer in channel, BER = 10 ⁻³	-6		dB
Selectivity, ±1MHz ⁽¹⁾	Wanted signal at –67dBm, modulated interferer at ±1MHz, BER = 10 ⁻³	7 / 4 ⁽²⁾		dB
Selectivity, ±2MHz ⁽¹⁾	Wanted signal at –67dBm, modulated interferer at ±2MHz,BER = 10 ⁻³	40 / 33 ⁽²⁾		dB
Selectivity, ±3MHz ⁽¹⁾	Wanted signal at –67dBm, modulated interferer at ±3MHz, BER = 10 ⁻³	36 / 41 ⁽²⁾		dB
Selectivity, ±4MHz ⁽¹⁾	Wanted signal at –67dBm, modulated interferer at ±4MHz, BER = 10 ⁻³	36 / 45 ⁽²⁾		dB
Selectivity, ±5MHz or more ⁽¹⁾	Wanted signal at –67dBm, modulated interferer at ≥ ±5MHz, BER = 10 ⁻³	40		dB
Selectivity, image frequency ⁽¹⁾	Wanted signal at –67dBm, modulated interferer at image frequency, BER = 10 ⁻³	33		dB
Selectivity, image frequency ±1MHz ⁽¹⁾	Note that Image frequency + 1MHz is the Co- channel – 1MHz. Wanted signal at –67dBm, modulated interferer at ±1MHz from image frequency, BER = 10^{-3}	4 / 41 ⁽²⁾		dB
Out-of-band blocking ⁽³⁾	30MHz to 2000MHz	-10		dBm
Out-of-band blocking	2003MHz to 2399MHz	-18		dBm
Out-of-band blocking	2484MHz to 2997MHz	-12		dBm
Out-of-band blocking	3000MHz to 12.75GHz	-2		dBm
Intermodulation	Wanted signal at 2402MHz, –64dBm. Two interferers at 2405 and 2408MHz respectively, at the given power level	-42		dBm
Spurious emissions, 30 to 1000MHz ⁽⁴⁾	Measurement in a 50 Ω single-ended load.	<-59		dBm
Spurious emissions, 1 to 12.75GHz ⁽⁴⁾	Measurement in a 50 Ω single-ended load.	<-47		dBm
RSSI dynamic range		70		dB
RSSI accuracy		±4		dB
2 Mbps (LE 2M)				
Receiver sensitivity	Differential mode. Measured at SMA connector, BER = 10 ⁻³	-92		dBm
Receiver saturation	Differential mode. Measured at SMA connector, BER = 10 ⁻³	> 5		dBm
Frequency error tolerance	Difference between the incoming carrier frequency and the internally generated carrier frequency	> (-500 / 500)		kHz
Data rate error tolerance	Difference between incoming data rate and the internally generated data rate (37-byte packets)	> (-700 / 750)		ppm



7.10 Bluetooth Low Energy—Receive (RX) (続き)

When measured on the LP-EM-CC1354P10-1 reference design with T_c = 25°C, V_{DDS} = 3.0V, f_{RF} = 2440MHz with DC/DC enabled unless otherwise noted. All measurements are performed at the antenna input with a combined RX and TX path. All measurements are performed conducted.

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Co-channel rejection ⁽¹⁾	Wanted signal at –67dBm, modulated interferer in channel,BER = 10 ⁻³		-7		dB
Selectivity, ±2MHz ⁽¹⁾	Wanted signal at –67dBm, modulated interferer at ±2MHz, Image frequency is at –2MHz, BER = 10 ⁻³		8 / 4 ⁽²⁾		dB
Selectivity, ±4MHz ⁽¹⁾	Wanted signal at –67dBm, modulated interferer at ±4MHz, BER = 10 ⁻³		35 / 32 ⁽²⁾		dB
Selectivity, ±6MHz ⁽¹⁾	Wanted signal at –67dBm, modulated interferer at ±6MHz, BER = 10 ⁻³		37 / 34 ⁽²⁾		dB
Selectivity, image frequency ⁽¹⁾	Wanted signal at –67dBm, modulated interferer at image frequency, BER = 10 ⁻³		4		dB
Selectivity, image frequency ±2MHz ⁽¹⁾	Note that Image frequency + 2MHz is the Co-channel. Wanted signal at –67dBm, modulated interferer at ±2MHz from image frequency, BER = 10 ⁻³		-7 / 36 ⁽²⁾		dB
Out-of-band blocking ⁽³⁾	30MHz to 2000MHz		-16		dBm
Out-of-band blocking	2003MHz to 2399MHz		-21		dBm
Out-of-band blocking	2484MHz to 2997MHz		-15		dBm
Out-of-band blocking	3000MHz to 12.75GHz		-20		dBm
Intermodulation	Wanted signal at 2402MHz, –64dBm. Two interferers at 2408 and 2414MHz respectively, at the given power level		-37		dBm
RSSI Range			64		dB
RSSI Accuracy (+/-)			±4		dB

- (1) Numbers given as I/C dB.
- (2) X / Y, where X is +N MHz and Y is -N MHz.
- (3) Excluding one exception at F_{wanted} / 2, per Bluetooth Specification.
- (4) Suitable for systems targeting compliance with worldwide radio-frequency regulations ETSI EN 300 328 and EN 300 440 Class 2 (Europe), FCC CFR47 Part 15 (US), and ARIB STD-T66 (Japan).

7.11 Bluetooth Low Energy—Transmit (TX)

When measured on the LP-EM-CC1354P10-1 reference design with $T_c = 25^{\circ}\text{C}$, $V_{DDS} = 3.0\text{V}$, $f_{RF} = 2440\text{MHz}$ with DC/DC enabled unless otherwise noted. All measurements are performed at the antenna input with a combined RX and TX path. All measurements are performed conducted.

PARAMETER		TEST CONDITIONS	MIN TY	P MAX	UNIT
General Parameters	•				
Max output power	Differential mode, delivered to a sing	le-ended 50Ω load through a balun		5	dBm
Output power programmable range	Differential mode, delivered to a sing)ifferential mode, delivered to a single-ended 50Ω load through a balun		6	dB
Spurious emissions a	and harmonics				
	f < 1GHz, outside restricted bands		< -3	6	dBm
Caurious amissions	f < 1GHz, restricted bands ETSI		< -5	4	dBm
Spurious emissions	f < 1GHz, restricted bands FCC	I EdDay actting	< -5	5	dBm
	f > 1GHz, including harmonics	_ +5dBm setting _	< -4	2	dBm
Harmaniaa	Second harmonic		< -4	2	dBm
Harmonics	Third harmonic		< -4	2	dBm

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7.12 Zigbee and Thread - IEEE 802.15.4-2006 2.4GHz (OQPSK DSSS1:8, 250kbps) - RX

When measured on the LP-EM-CC1354P10-1 reference design with T_c = 25°C, V_{DDS} = 3.0V, f_{RF} = 2440MHz with DC/DC enabled unless otherwise noted. All measurements are performed at the antenna input with a combined RX and TX path. All measurements are performed conducted.

PARAMETER	TEST CONDITIONS	MIN TYP MAX	UNIT
General Parameters			
Receiver sensitivity	Coherent mode PER = 1%	-105	dBm
Receiver saturation	PER = 1%	> -10	dBm
Adjacent channel rejection	Wanted signal at –82dBm, modulated interferer at ±5MHz, PER = 1%	36	dB
Alternate channel rejection	Wanted signal at –82dBm, modulated interferer at ±10MHz, PER = 1%	55	dB
Channel rejection, ±15MHz or more	Wanted signal at –82dBm, undesired signal is IEEE 802.15.4 modulated channel, stepped through all channels 2405 to 2480MHz, PER = 1%	59	dB
Blocking and desensitization, 5MHz from upper band edge	Wanted signal at 3 dB above the sensitivity level, CW jammer, PER = 1%	57	dB
Blocking and desensitization, 10MHz from upper band edge	Wanted signal at 3 dB above the sensitivity level, CW jammer, PER = 1%	62	dB
Blocking and desensitization, 20MHz from upper band edge	Wanted signal at 3 dB above the sensitivity level, CW jammer, PER = 1%	62	dB
Blocking and desensitization, 50MHz from upper band edge	Wanted signal at 3 dB above the sensitivity level, CW jammer, PER = 1%	65	dB
Blocking and desensitization, –5MHz from lower band edge	Wanted signal at 3 dB above the sensitivity level, CW jammer, PER = 1%	60	dB
Blocking and desensitization, –10MHz from lower band edge	Wanted signal at 3 dB above the sensitivity level, CW jammer, PER = 1%	60	dB
Blocking and desensitization, –20MHz from lower band edge	Wanted signal at 3 dB above the sensitivity level, CW jammer, PER = 1%	60	dB
Blocking and desensitization, –50MHz from lower band edge	Wanted signal at 3 dB above the sensitivity level, CW jammer, PER = 1%	62	dB
Spurious emissions, 30MHz to 1000MHz	Measurement in a 50 Ω single-ended load	-66	dBm
Spurious emissions, 1GHz to 12.75GHz	Measurement in a 50 Ω single-ended load	-53	dBm
Frequency error tolerance	Difference between the incoming carrier frequency and the internally generated carrier frequency	> 100	ppm
Symbol rate error tolerance	Difference between incoming symbol rate and the internally generated symbol rate	> 800	ppm
RSSI dynamic range		95	dB
RSSI accuracy		±4	dB

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7.13 Zigbee and Thread - IEEE 802.15.4-2006 2.4GHz (OQPSK DSSS1:8, 250kbps) - TX

When measured on the LP-EM-CC1354P10-1 reference design with T_c = 25°C, V_{DDS} = 3.0V, f_{RF} = 2440MHz with DC/DC enabled unless otherwise noted. All measurements are performed at the antenna input with a combined RX and TX path. All measurements are performed conducted.

PARAMETER		TEST CONDITIONS	MIN TYP	MAX	UNIT
General Parameters					
Max output power	Differential mode, delivered to a si	ngle-ended 50 Ω load through a balun	5		dBm
Output power programmable range	Differential mode, delivered to a si	ngle-ended 50 Ω load through a balun	26		dB
Spurious emissions and	harmonics				
	f < 1GHz, outside restricted bands		< -36		dBm
Spurious emissions	f < 1GHz, restricted bands ETSI		< -47		dBm
	f < 1GHz, restricted bands FCC	+5dBm setting	< -55		dBm
	f > 1GHz, including harmonics	_	< -42		dBm
Harmonics	Second harmonic		< -42		dBm
Harmonics	Third harmonic		< -42		dBm
IEEE 802.15.4-2006 2.4G	Hz (OQPSK DSSS1:8, 250kbps)		•		
Error vector magnitude	+5dBm setting		2		%

7.14 Timing and Switching Characteristics

7.14.1 Reset Timing

PARAMETER	MIN	TYP	MAX	UNIT
RESET_N low duration	1			μs

7.14.2 Wakeup Timing

Measured over operating free-air temperature with V_{DDS} = 3.0V (unless otherwise noted). The times listed here do not include software overhead.

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
MCU, Reset to Active ⁽¹⁾		8	50 - 4000		μs
MCU, Shutdown to Active ⁽¹⁾		8	50 - 4000		μs
MCU, Standby to Active			160		μs
MCU, Active to Standby			39		μs
MCU, Idle to Active			15		μs

(1) The wakeup time is dependent on remaining charge on VDDR capacitor when starting the device, and thus how long the device has been in Reset or Shutdown before starting up again. The wake up time increases with a higher capacitor value.

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7.14.3 Clock Specifications

7.14.3.1 48MHz Crystal Oscillator (XOSC_HF)

Measured on a Texas Instruments reference design with T_c = 25°C, V_{DDS} = 3.0V, unless otherwise noted.⁽¹⁾

	PARAMETER	MIN	TYP	MAX	UNIT
F	Crystal frequency		48		MHz
ESR	Equivalent series resistance 6 pF < C _L ≤ 9 pF		20	60	Ω
ESR	Equivalent series resistance 5 pF < C _L ≤ 6 pF			80	Ω
L _M	Motional inductance, relates to the load capacitance that is used for the crystal (C _L in Farads) ⁽²⁾		< 3 × 10 ⁻²⁵ / C _L ²		Н
C _L	Crystal load capacitance ⁽³⁾	5	7 ⁽⁴⁾	9	pF
t	Start-up time ⁽⁵⁾		200		μs

- (1) Probing or otherwise stopping the crystal while the DC/DC converter is enabled may cause permanent damage to the device.
- (2) The crystal manufacturer's specification must satisfy this requirement for proper operation.
- (3) Adjustable load capacitance is integrated into the device.
- (4) On-chip default connected capacitance including reference design parasitic capacitance. Connected internal capacitance is changed through software in the Customer Configuration section (CCFG).
- (5) Start-up time using the TI-provided power driver. Start-up time may increase if driver is not used.

7.14.3.2 48MHz RC Oscillator (RCOSC_HF)

Measured on a Texas Instruments reference design with T_c = 25°C, V_{DDS} = 3.0V, unless otherwise noted.

	MIN	TYP	MAX	UNIT
Frequency		48		MHz
Uncalibrated frequency accuracy		±1		%
Calibrated frequency accuracy ⁽¹⁾		±0.25		%
Start-up time		5		μs

(1) Accuracy relative to the calibration source (XOSC_HF).

7.14.3.3 2MHz RC Oscillator (RCOSC_MF)

Measured on a Texas Instruments reference design with T_c = 25°C, V_{DDS} = 3.0V, unless otherwise noted.

	MIN	TYP	MAX	UNIT
Calibrated frequency		2		MHz
Start-up time		5		μs

7.14.3.4 32.768 kHz Crystal Oscillator (XOSC_LF)

Measured on a Texas Instruments reference design with T_c = 25°C, V_{DDS} = 3.0V, unless otherwise noted.

		MIN	TYP	MAX	UNIT
	Crystal frequency		32.768		kHz
ESR	Equivalent series resistance		30	100	kΩ
C _L	Crystal load capacitance	6	7 ⁽¹⁾	12	pF

¹⁾ Default load capacitance using TI reference designs including parasitic capacitance. Crystals with different load capacitance may be used

7.14.3.5 32 kHz RC Oscillator (RCOSC_LF)

Measured on a Texas Instruments reference design with T_c = 25°C, V_{DDS} = 3.0V, unless otherwise noted.

	MIN	TYP	MAX	UNIT
Calibrated frequency		32.8 (1)		kHz

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7.14.3.5 32 kHz RC Oscillator (RCOSC LF) (続き)

Measured on a Texas Instruments reference design with $T_c = 25$ °C, $V_{DDS} = 3.0$ V, unless otherwise noted.

	MIN	TYP	MAX	UNIT
Temperature coefficient.		50		ppm/°C

(1) When using RCOSC_LF as source for the low frequency system clock (SCLK_LF), the accuracy of the SCLK_LF-derived Real Time Clock (RTC) can be improved by measuring RCOSC_LF relative to XOSC_HF and compensating for the RTC tick speed. This functionality is available through the TI-provided Power driver.

7.14.4 Serial Peripheral Interface (SPI) Characteristics

7.14.4.1 SPI Characteristics

over operating free-air temperature range (unless otherwise noted).

	PARAMETERS	TEST CONDITIONS	MIN	TYP	MAX	UNIT
		Master Mode 1.8 < VDDS < 3.8			12	
f _{SCLK} 1/t _{sclk}	SPI clock frequency	Slave Mode 2.7 < VDDS < 3.8			8	MHz
		Slave Mode VDDS < 2.7			7	
DC _{SCK}	SCK Duty Cycle		45	50	55	%

7.14.4.2 SPI Master Mode

over operating free-air temperature range (unless otherwise noted).

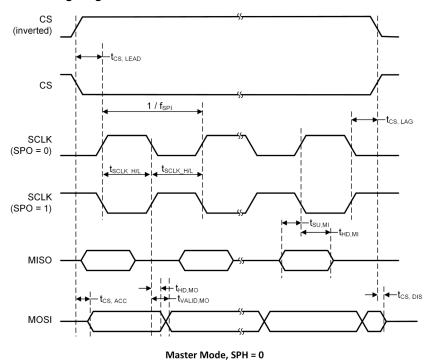
	PARAMETERS	TEST CONDITIONS	MIN	TYP M	AX	UNIT
t _{SCLK_H/}	SCLK High or Low time		(t _{SPI} /2) - 1	t _{SPI} / 2 (t _{SPI} /2)	+ 1	ns
t _{CS.LEAD}	CS lead-time, CS active to clock		1			SCLK
t _{CS.LAG}	CS lag time, Last clock to CS inactive		1			SCLK
t _{CS.ACC}	CS access time, CS active to MOSI data out				1	SCLK
t _{CS.DIS}	CS disable time, CS inactive to MOSI high inpedance				1	SCLK
t _{SU.MI}	MISO input data setup time(1)	VDDS = 3.3V	12.5			ns
t _{SU.MI}	MISO input data setup time	VDDS = 1.8V	23.5			ns
t _{HD.MI}	MISO input data hold time		0			ns
t _{VALID.M}	MOSI output data valid time ⁽²⁾	SCLK edge to MOSI valid,CL = 20 pF (4)			13	ns
t _{HD.MO}	MOSI output data hold time(3)	CL = 20 pF	0			ns

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- (1) The MISO input data setup time can be fully compensated when delayed sampling feature is enabled.
- (2) Specifies the time to drive the next valid data to the output after the output changing SCLK clock edge.
- (3) Specifies how long data on the output is valid after the output changing SCLK clock edge.

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7.14.4.3 SPI Master Mode Timing Diagrams



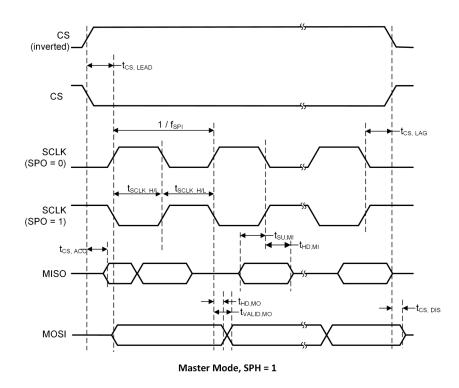


図 7-1. SPI Master Mode Timing

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7.14.4.4 SPI Slave Mode

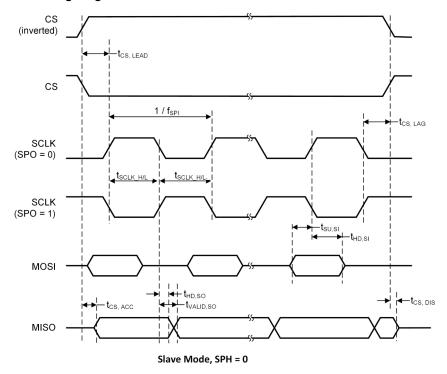
over operating free-air temperature range (unless otherwise noted).

	PARAMETERS	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _{CS.LEAD}	CS lead-time, CS active to clock		1			SCLK
t _{CS.LAG}	CS lag time, Last clock to CS inactive		1			SCLK
t _{CS.ACC}	CS access time, CS active to MISO data out	VDDS = 3.3V			56	ns
t _{CS.ACC}	CS access time, CS active to MISO data out	VDDS = 1.8V			70	ns
t _{CS.DIS}	CS disable time, CS inactive to MISO high inpedance	VDDS = 3.3V			56	ns
t _{CS.DIS}	CS disable time, CS inactive to MISO high inpedance	VDDS = 1.8V			70	ns
t _{SU.SI}	MOSI input data setup time		30			ns
t _{HD.SI}	MOSI input data hold time		0			ns
t _{VALID.S}	MISO output data valid time ⁽¹⁾	SCLK edge to MISO valid,C _L = 20 pF, 3.3V (4)			50	ns
t _{VALID.S}	MISO output data valid time ⁽¹⁾	SCLK edge to MISO valid,C _L = 20 pF, 1.8V (4)			65	ns
t _{HD.SO}	MISO output data hold time(2)	C _L = 20 pF	0			ns

⁽¹⁾ Specifies the time to drive the next valid data to the output after the output changing SCLK clock edge.

⁽²⁾ Specifies how long data on the output is valid after the output changing SCLK clock edge.

7.14.4.5 SPI Slave Mode Timing Diagrams



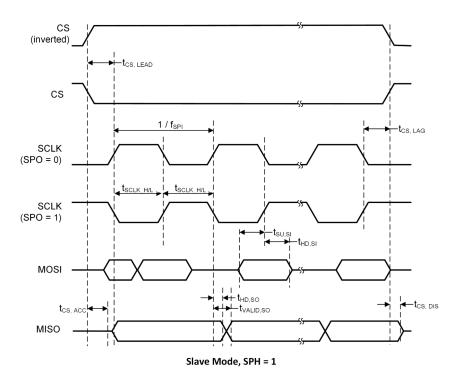


図 7-2. SPI Slave Mode Timing

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7.14.5 UART

7.14.5.1 UART Characteristics

over operating free-air temperature range (unless otherwise noted).

PARAMETER	MIN	TYP	MAX	UNIT
UART rate			3	MBaud

7.15 Peripheral Characteristics

7.15.1 ADC

7.15.1.1 Analog-to-Digital Converter (ADC) Characteristics

 T_c = 25°C, V_{DDS} = 3.0V and voltage scaling enabled, unless otherwise noted.⁽¹⁾ Performance numbers require use of offset and gain adjustements in software by TI-provided ADC drivers.

	PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
	Input voltage range		0	VDDS	V
	Resolution		12		Bits
	Sample Rate			200	ksps
	Offset	Internal 4.3V equivalent reference ⁽²⁾	-0.24		LSB
	Gain error	Internal 4.3V equivalent reference ⁽²⁾	7.14		LSB
DNL ⁽³⁾	Differential nonlinearity		>-1		LSB
INL	Integral nonlinearity		±4		LSB
		Internal 4.3V equivalent reference ⁽²⁾ , 200 kSamples/s, 9.6kHz input tone	9.8		
		Internal 4.3V equivalent reference ⁽²⁾ , 200 kSamples/s, 9.6kHz input tone, DC/DC enabled	9.8		
		VDDS as reference, 200 kSamples/s, 9.6kHz input tone	10.1		
ENOB	Effective number of bits	Internal reference, voltage scaling disabled, 32 samples average, 200 kSamples/s, 300Hz input tone	11.1		Bits
		Internal reference, voltage scaling disabled, 14-bit mode, 200 kSamples/s, 300Hz input tone ⁽⁴⁾	11.3		
		Internal reference, voltage scaling disabled, 15-bit mode, 200 kSamples/s, 300Hz input tone ⁽⁴⁾	11.6		
	Total harmonic distortion	Internal 4.3V equivalent reference ⁽²⁾ , 200 kSamples/s, 9.6kHz input tone	-65		
THD		VDDS as reference, 200 kSamples/s, 9.6kHz input tone	-70		dB
		Internal reference, voltage scaling disabled, 32 samples average, 200 kSamples/s, 300Hz input tone	-72		
	Signal-to-noise	Internal 4.3V equivalent reference ⁽²⁾ , 200 kSamples/s, 9.6kHz input tone	60		
SINAD, SNDR	and	VDDS as reference, 200 kSamples/s, 9.6kHz input tone	63		dB
ONDIN	distortion ratio	Internal reference, voltage scaling disabled, 32 samples average, 200 kSamples/s, 300Hz input tone	68		
		Internal 4.3V equivalent reference ⁽²⁾ , 200 kSamples/s, 9.6kHz input tone	70		
SFDR	Spurious-free dynamic range	VDDS as reference, 200 kSamples/s, 9.6kHz input tone	73		dB
		Internal reference, voltage scaling disabled, 32 samples average, 200 kSamples/s, 300Hz input tone	75		
	Conversion time	Serial conversion, time-to-output, 24MHz clock	50		Clock Cycles
	Current consumption	Internal 4.3V equivalent reference ⁽²⁾	0.42		mA
	Current consumption	VDDS as reference	0.6		mA
	Reference voltage	Equivalent fixed internal reference (input voltage scaling enabled). For best accuracy, the ADC conversion should be initiated through the TI-RTOS API in order to include the gain/ offset compensation factors stored in FCFG1	4.3(2) (5)		V

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7.15.1.1 Analog-to-Digital Converter (ADC) Characteristics (続き)

 T_c = 25°C, V_{DDS} = 3.0V and voltage scaling enabled, unless otherwise noted.⁽¹⁾

Performance numbers require use of offset and gain adjustements in software by TI-provided ADC drivers.

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Reference voltage	Fixed internal reference (input voltage scaling disabled). For best accuracy, the ADC conversion should be initiated through the TI-RTOS API in order to include the gain/offset compensation factors stored in FCFG1. This value is derived from the scaled value (4.3V) as follows: $V_{\text{ref}} = 4.3\text{V} \times 1408 / 4095$		1.48		V
Reference voltage	VDDS as reference, input voltage scaling enabled		VDDS		V
Reference voltage VDDS as reference, input voltage scaling disabled VDDS / 2.82 ⁽⁵⁾				V	
Input impedance	200 kSamples/s, voltage scaling enabled. Capacitive input, Input impedance depends on sampling frequency and sampling time		>1		ΜΩ

⁽¹⁾ Using IEEE Std 1241-2010 for terminology and test methods.

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⁽²⁾ Input signal scaled down internally before conversion, as if voltage range was 0V to 4.3V.

⁽³⁾ No missing codes.

⁽⁴⁾ ADC output = $\Sigma(4^n \text{ samples}) >> n$, n = desired extra bits.

⁽⁵⁾ Applied voltage must be within Absolute Maximum Ratings at all times.



7.15.2 DAC

7.15.2.1 Digital-to-Analog Converter (DAC) Characteristics

 $T_c = 25$ °C, $V_{DDS} = 3.0$ V, unless otherwise noted.

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
enera	I Parameters					
	Resolution			8		Bits
		Any load, any V _{REF} , pre-charge OFF, DAC charge-pump ON	1.8		3.8	
/ _{DDS}	Supply voltage	External Load ⁽¹⁾ , any V _{REF} , pre-charge OFF, DAC charge-pump OFF	2.0		3.8	V
		Any load, V _{REF} = DCOUPL, pre-charge ON	2.6		3.8	
	Clask fraguency	Buffer ON (recommended for external load)	16		250	ld la
DAC	Clock frequency	Buffer OFF (internal load)	16		1000	kHz
	Voltage output settling time	V _{REF} = VDDS, buffer OFF, internal load		13		1/5
	Voltage output settling time	V _{REF} = VDDS, buffer ON, external capacitive load = 20pF ⁽²⁾		13.8		1/F _{DAC}
	External capacitive load			20	200	pF
	External resistive load		10			ΜΩ
	Short circuit current				400	μA
		VDDS = 3.8V, DAC charge-pump OFF		50.8		
		VDDS = 3.0V, DAC charge-pump ON		51.7		
	Max output impedance Vref =	VDDS = 3.0V, DAC charge-pump OFF		53.2		
Z _{MAX}	VDDS, buffer ON, CLK 250kHz	VDDS = 2.0 V, DAC charge-pump ON		48.7		kΩ
		VDDS = 2.0 V, DAC charge-pump OFF		70.2		
		VDDS = 1.8V, DAC charge-pump ON		46.3		
		VDDS = 1.8V, DAC charge-pump OFF		88.9		
nterna	Load - Continuous Time Com	parator / Low Power Clocked Comparator				
DAU	Differential nonlinearity	V _{REF} = VDDS, load = Continuous Time Comparator or Low Power Clocked Comparator F _{DAC} = 250kHz		±1		1.00(3)
DNL	Differential nonlinearity	V _{REF} = VDDS, load = Continuous Time Comparator or Low Power Clocked Comparator F _{DAC} = 16 kHz		±1.2		LSB ⁽³⁾
		V _{REF} = VDDS = 3.8V		±0.64		
		V _{REF} = VDDS = 3.0V		±0.81		
	Offset error ⁽⁴⁾	V _{REF} = VDDS = 1.8V		±1.27		(2)
	Load = Continuous Time Comparator	V _{REF} = DCOUPL, pre-charge ON		±3.43		LSB ⁽³⁾
		V _{REF} = DCOUPL, pre-charge OFF		±2.88		
		V _{REF} = ADCREF		±2.37		
		V _{REF} = VDDS = 3.8V		±0.78		
		V _{REF} = VDDS = 3.0V		±0.77		
	Offset error ⁽⁴⁾	V _{REF} = VDDS = 1.8V		±3.46		(0)
	Load = Low Power Clocked Comparator	V _{REF} = DCOUPL, pre-charge ON		±3.44		LSB ⁽³⁾
	Comparator	V _{RFF} = DCOUPL, pre-charge OFF		±4.70		
		V _{RFF} = ADCREF		±4.11		
		V _{REF} = VDDS = 3.8V		±1.53		
		V _{REF} = VDDS = 3.0V		±1.71		
	Max code output voltage variation ⁽⁴⁾	V _{RFF} = VDDS = 1.8V		±2.10		
	variation ⁽⁴⁾ Load = Continuous Time Comparator	V _{REF} = DCOUPL, pre-charge ON		±6.00		LSB ⁽³⁾
	Comparator	V _{REF} = DCOUPL, pre-charge OFF		±3.85		



7.15.2.1 Digital-to-Analog Converter (DAC) Characteristics (続き)

 $T_c = 25$ °C, $V_{DDS} = 3.0$ V, unless otherwise noted.

	PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
		V _{REF} = VDDS = 3.8V	±2.92		
	Managada autoutusitassa	V _{REF} =VDDS = 3.0V	±3.06		
	Max code output voltage variation ⁽⁴⁾	V _{REF} = VDDS = 1.8V	±3.91		LSB ⁽³⁾
	Load = Low Power Clocked Comparator	V _{REF} = DCOUPL, pre-charge ON	±7.84		LOB
	Comparator	V _{REF} = DCOUPL, pre-charge OFF	±4.06		
		V _{REF} = ADCREF	±6.94		
		V _{REF} = VDDS = 3.8V, code 1	0.03		
		V _{REF} = VDDS = 3.8V, code 255	3.62		
		V _{REF} = VDDS = 3.0V, code 1	0.02		
		V _{REF} = VDDS = 3.0V, code 255	2.86		
		V _{REF} = VDDS = 1.8V, code 1	0.01		
	Output voltage range ⁽⁴⁾ Load = Continuous Time	V _{REF} = VDDS = 1.8V, code 255	1.71		V
	Comparator	V _{REF} = DCOUPL, pre-charge OFF, code 1	0.01		V
		V _{REF} = DCOUPL, pre-charge OFF, code 255	1.21		
		V _{REF} = DCOUPL, pre-charge ON, code 1	1.27		
		V _{REF} = DCOUPL, pre-charge ON, code 255	2.46		
		V _{REF} = ADCREF, code 1	0.01		
		V _{REF} = ADCREF, code 255	1.41		
		V _{REF} = VDDS = 3.8V, code 1	0.03		
	Output voltage range ⁽⁴⁾	V _{REF} = VDDS = 3.8V, code 255	3.61		
		V _{REF} = VDDS = 3.0V, code 1	0.02		
		V _{REF} = VDDS = 3.0V, code 255	2.85		
		V _{REF} = VDDS = 1.8V, code 1	0.01		
		V _{REF} = VDDS = 1.8V, code 255	1.71		.,
	Load = Low Power Clocked Comparator	V _{REF} = DCOUPL, pre-charge OFF, code 1	0.01		V
		V _{REF} = DCOUPL, pre-charge OFF, code 255	1.21		
		V _{REF} = DCOUPL, pre-charge ON, code 1	1.27		
		V _{REF} = DCOUPL, pre-charge ON, code 255	2.46		
		V _{REF} = ADCREF, code 1	0.01		
		V _{REF} = ADCREF, code 255	1.41		
ktern	al Load (Keysight 34401A Mul	timeter)			
		V _{REF} = VDDS, F _{DAC} = 250kHz	±1		
۱L	Integral nonlinearity	V _{REF} = DCOUPL, F _{DAC} = 250kHz	±1		LSB ⁽³⁾
		V _{REF} = ADCREF, F _{DAC} = 250kHz	±1		
NL	Differential nonlinearity	V _{REF} = VDDS, F _{DAC} = 250kHz	±1		LSB ⁽³⁾
		V _{REF} = VDDS = 3.8V	±0.20		
		V _{REF} = VDDS = 3.0V	±0.25		
		V _{REF} = VDDS = 1.8V	±0.45		(2)
	Offset error	V _{REF} = DCOUPL, pre-charge ON	±1.55		LSB ⁽³⁾
		V _{REF} = DCOUPL, pre-charge OFF	±1.30		
		V _{REF} = ADCREF	±1.10		
		V _{REF} = VDDS = 3.8V	±0.60		
		V _{REF} = VDDS = 3.0V	±0.55		
	Max code output voltage	V _{REF} = VDDS = 1.8V	±0.60		(0)
	variation	V _{REF} = DCOUPL, pre-charge ON	±3.45		LSB ⁽³⁾
		V _{REF} = DCOUPL, pre-charge OFF	±2.10		
		V _{REF} = ADCREF	±1.90		



7.15.2.1 Digital-to-Analog Converter (DAC) Characteristics (続き)

 T_c = 25°C, V_{DDS} = 3.0V, unless otherwise noted.

PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
	V _{REF} = VDDS = 3.8V, code 1	0.03		
	V _{REF} = VDDS = 3.8V, code 255	3.61		
	V _{REF} = VDDS = 3.0V, code 1	0.02		
	V _{REF} = VDDS = 3.0V, code 255	2.85		
	V _{REF} = VDDS = 1.8V, code 1	0.02		
Output voltage range Load = Low Power Clocked Comparator	V _{REF} = VDDS = 1.8V, code 255	1.71		V
	V _{REF} = DCOUPL, pre-charge OFF, code 1	0.02		V
	V _{REF} = DCOUPL, pre-charge OFF, code 255	1.20		
	V _{REF} = DCOUPL, pre-charge ON, code 1	1.27		
	V _{REF} = DCOUPL, pre-charge ON, code 255	2.46		
	V _{REF} = ADCREF, code 1	0.02		
	V _{REF} = ADCREF, code 255	1.42		

- (1) Keysight 34401A Multimeter.
- A load > 20pF increincreasesettling time. 1 LSB (V_{REF} 3.8V/3.0V/1.8V/DCOUPL/ADCREF) = 14.10mV/11.13mV/6.68mV/4.67mV/5.48mV.
- Includes comparator offset.



7.15.3 Temperature and Battery Monitor

7.15.3.1 Temperature Sensor

Measured on a Texas Instruments reference design with T_c = 25°C, V_{DDS} = 3.0V, unless otherwise noted.

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Resolution			2		°C
Accuracy	-40°C to 0°C		±5.0		°C
Accuracy	0°C to 105 °C		±3.5		°C
Supply voltage coefficient ⁽¹⁾			3.6		°C/V

⁽¹⁾ The temperature sensor is automatically compensated for VDDS variation when using the TI-provided driver.

7.15.3.2 Battery Monitor

Measured on a Texas Instruments reference design with T_c = 25°C, unless otherwise noted.

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Resolution			25		mV
Range		1.8		3.8	V
Integral nonlinearity (max)			23		mV
Accuracy	VDDS = 3.0V		22.5		mV
Offset error			-32		mV
Gain error			-1		%

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7.15.4 Comparators

7.15.4.1 Low-Power Clocked Comparator

 $T_c = 25$ °C, $V_{DDS} = 3.0$ V, unless otherwise noted.

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Input voltage range		0		V _{DDS}	V
Clock frequency			SCLK_LF		
Internal reference voltage ⁽¹⁾	Using internal DAC with VDDS as reference voltage, DAC code = 0 - 255		0.024 - 2.865		V
Offset	Measured at V _{DDS} / 2, includes error from internal DAC		±5		mV
Decision time	Step from –50 mV to 50 mV		1		Clock Cycle

⁽¹⁾ The comparator can use an internal 8 bits DAC as its reference. The DAC output voltage range depends on the reference voltage selected. See DAC Characteristics.

7.15.4.2 Continuous Time Comparator

 $T_c = 25$ °C, $V_{DDS} = 3.0$ V, unless otherwise noted.

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Input voltage range ⁽¹⁾		0		V_{DDS}	V
Offset	Measured at V _{DDS} / 2		±5		mV
Decision time	Step from –10mV to 10mV		0.78		μs
Current consumption	Internal reference		8.6		μA

⁽¹⁾ The input voltages can be generated externally and connected throughout I/Os or an internal reference voltage can be generated using the DAC.

7.15.5 Current Source

7.15.5.1 Programmable Current Source

 $T_c = 25$ °C, $V_{DDS} = 3.0$ V, unless otherwise noted.

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Current source programmable output range (logarithmic range)			0.25 - 20		μΑ
Resolution			0.25		μΑ

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7.15.6 GPIO

7.15.6.1 GPIO DC Characteristics

PARAMETER	TEST CONDITIONS	MIN TYP MAX	UNIT
T _A = 25°C, V _{DDS} = 1.8V			
GPIO VOH at 8mA load	IOCURR = 2, high-drive GPIOs only	1.56	V
GPIO VOL at 8mA load	IOCURR = 2, high-drive GPIOs only	0.24	V
GPIO VOH at 4mA load	IOCURR = 1	1.59	V
GPIO VOL at 4mA load	IOCURR = 1	0.21	V
GPIO pullup current	Input mode, pullup enabled, Vpad = 0 V	73	μA
GPIO pulldown current	Input mode, pulldown enabled, Vpad = VDDS	19	μA
GPIO low-to-high input transition, with hysteresis	IH = 1, transition voltage for input read as $0 \rightarrow 1$	1.08	V
GPIO high-to-low input transition, with hysteresis	IH = 1, transition voltage for input read as $1 \rightarrow 0$	0.73	V
GPIO input hysteresis	IH = 1, difference between $0 \rightarrow 1$ and $1 \rightarrow 0$ points	0.35	V
T _A = 25°C, V _{DDS} = 3.0V			
GPIO VOH at 8mA load	IOCURR = 2, high-drive GPIOs only	2.59	V
GPIO VOL at 8mA load	IOCURR = 2, high-drive GPIOs only	0.42	V
GPIO VOH at 4mA load	IOCURR = 1	2.63	V
GPIO VOL at 4mA load	IOCURR = 1	0.40	V
T _A = 25°C, V _{DDS} = 3.8V			
GPIO pullup current	Input mode, pullup enabled, Vpad = 0 V	282	μA
GPIO pulldown current	Input mode, pulldown enabled, Vpad = VDDS	110	μA
GPIO low-to-high input transition, with hysteresis	IH = 1, transition voltage for input read as $0 \rightarrow 1$	1.97	V
GPIO high-to-low input transition, with hysteresis	IH = 1, transition voltage for input read as $1 \rightarrow 0$	1.55	V
GPIO input hysteresis	IH = 1, difference between $0 \rightarrow 1$ and $1 \rightarrow 0$ points	0.42	V
T _A = 25°C	- 1		'
VIH	Lowest GPIO input voltage reliably interpreted as a High	0.8*V _{DDS}	V
VIL	Highest GPIO input voltage reliably interpreted as a Low	0.2*V _{DD}	, V

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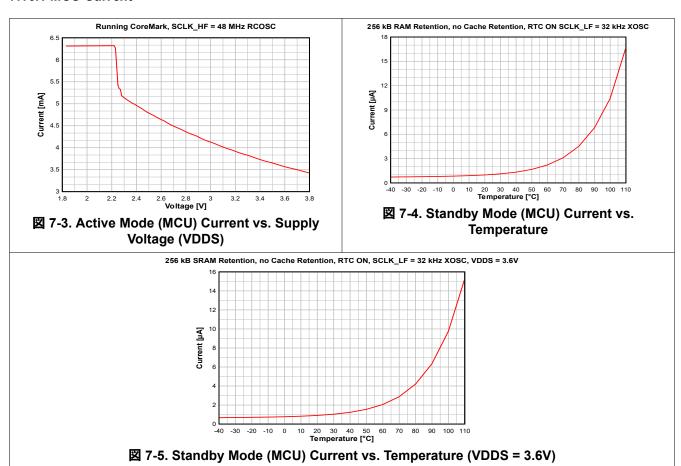
Product Folder Links: CC2674R10



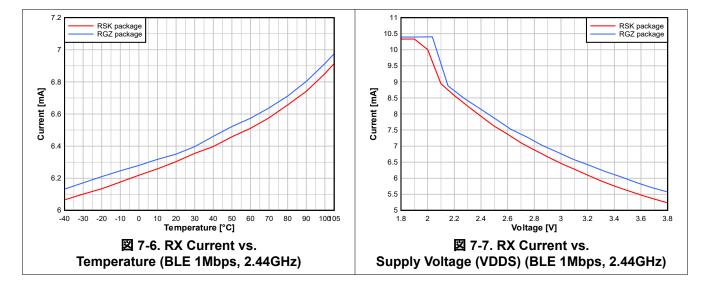
7.16 Typical Characteristics

All measurements in this section are done with T_c = 25°C and V_{DDS} = 3.0V, unless otherwise noted. See *Recommended Operating Conditions*, $\forall 2/2 \forall 3/2 \forall$

7.16.1 MCU Current



7.16.2 RX Current



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7.16.3 TX Current

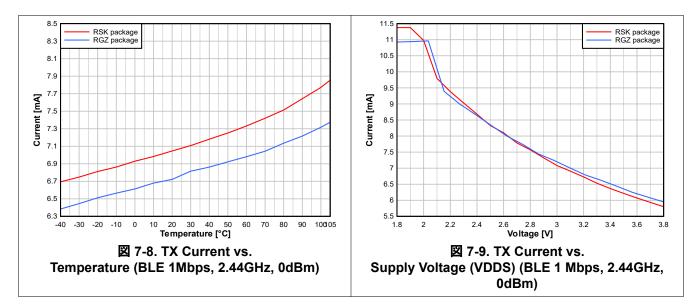
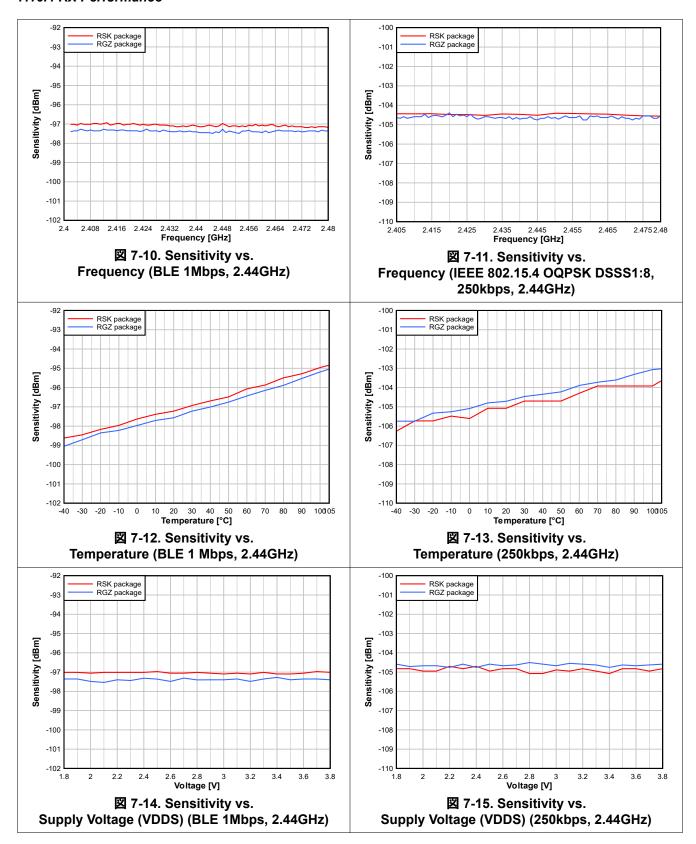


表 7-1. Typical TX Current and Output Power

CC2674R10 at 2.4GHz, VDDS = 3.0V (Measured on CC1352-7PEM-XD7793-XD24-PA24)			
txPower	TX Power Setting (SmartRF Studio)	Typical Output Power [dBm]	Typical Current Consumption [mA]
0x762E	5	4.7	10
0x8220	4	3.7	9
0x5617	3	2.8	8
0x3E66	2	1.9	8
0x3261	1	0.9	8
0x2C5D	0	0.0	7
0x1899	-3	-3.1	6
0x1695	-5	-4.9	6
0x1693	-6	-6.0	6
0x0CD4	-9	-9.1	5
0x0AD3	-10	-9.8	5
0x0AD0	-12	-11.9	5
0x06CD	-15	-14.6	5
0x04CA	-18	-17.8	5
0x04C8	-20	-20.4	4

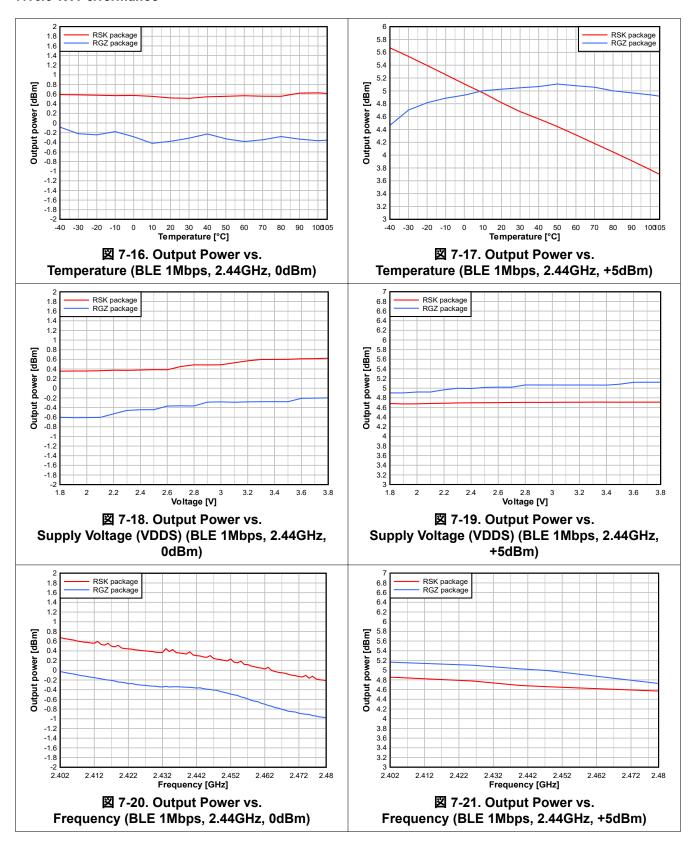


7.16.4 RX Performance



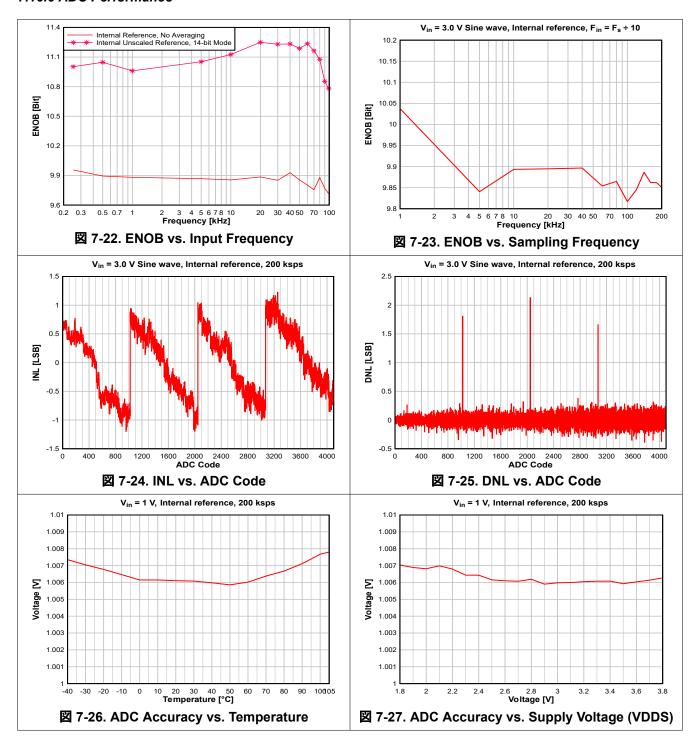


7.16.5 TX Performance





7.16.6 ADC Performance





8 Detailed Description

8.1 Overview

CC2674R10 ブロック図 shows the core modules of the CC2674R10 device.

Throughout this section, see the Technical Reference Manual listed in Section 11.2 for more details.

8.2 System CPU

The CC2674R10 SimpleLink[™] Wireless MCU contains an Arm[®] Cortex[®]-M33 system CPU with TrustZone[®], which runs the application and the higher layers of radio protocol stacks.

The system CPU is the foundation of a high-performance, low-cost platform that meets the system requirements of minimal memory implementation, and low power consumption while delivering outstanding computational performance and exceptional system response to interrupts.

Its features include the following:

- ARMv8-M architecture with TrustZone[®] security extension optimized for small-footprint embedded applications
- Arm Thumb®-2 mixed 16- and 32-bit instruction set delivers the high performance expected of a 32-bit Arm
 core in a compact memory size
- 8 regions of non-secure memory-protected regions
- 8 regions of secure memory-protected regions
- 4 regions of Security Attribute Unit (SAU)
- · Single-cycle multiply instruction and hardware divide
- · Digital signal processing (DSP) extension
- IEEE 754-compliant single-precision Floating Point Unit (FPU)
- Fast code execution permits increased sleep mode time
- Deterministic, high-performance interrupt handling for time-critical applications
- Full debug with data matching for watchpoint generation
 - Data Watchpoint and Trace Unit (DWT)
 - JTAG Debug Access Port (DAP)
 - Flash Patch and Breakpoint Unit (FPB)
- Trace support reduces the number of pins required for debugging and tracing
 - Instrumentation Trace Macrocell Unit (ITM)
 - Trace Port Interface Unit (TPIU) with asynchronous serial wire output (SWO)
- Optimized for single-cycle flash memory access
- Tightly connected to 8kB 4-way random replacement cache for minimal active power consumption and wait states

Product Folder Links: CC2674R10

- Ultra-low-power consumption with integrated sleep modes
- · 48MHz operation

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8.3 Radio (RF Core)

The RF Core is a highly flexible and future-proof radio module that contains an Arm Cortex-M0 processor that interfaces the analog RF and base-band circuitry, handles data to and from the system CPU side, and assembles the information bits in a given packet structure. The RF core offers a high-level, command-based API to the main CPU that configurations and data are passed through. The Arm Cortex-M0 processor is not programmable by customers and is interfaced through the TI-provided RF driver that is included with the SimpleLink Software Development Kit (SDK).

The RF core can autonomously handle the time-critical aspects of the radio protocols, thus offloading the main CPU, which reduces power and leaves more resources for the user application. Several signals are also available to control external circuitry such as RF switches or range extenders autonomously.

The various physical layer radio formats are partly built as a software-defined radio where the radio behavior is either defined by radio ROM contents or by non-ROM radio formats delivered in the form of firmware patches with the SimpleLink SDKs. This allows the radio platform to be updated for support of future versions of standards even with over-the-air (OTA) updates while still using the same silicon.

8.3.1 Bluetooth 5.3 Low Energy

The RF Core offers full support for Bluetooth 5.3 Low Energy, including the high-speed 2Mbps physical layer and the 500kbps and 125kbps long-range PHYs (coded PHY) through the TI-provided Bluetooth 5.3 stack or a high-level Bluetooth API. The Bluetooth 5.3 PHY and part of the controller are in radio and system ROM, providing significant savings in memory usage and more space available for applications.

The new high-speed mode allows data transfers up to 2Mbps, twice the speed of Bluetooth 4.2 and five times the speed of Bluetooth 4.0, without increasing power consumption. In addition to faster speeds, this mode offers significant improvements for energy efficiency and wireless coexistence with reduced radio communication time.

Bluetooth 5.3 also enables unparalleled flexibility for adjustment of speed and range based on application needs, which capitalizes on the high-speed or long-range modes respectively. Data transfers are now possible at 2Mbps, enabling the development of applications using voice, audio, imaging, and data logging that were not previously an option using Bluetooth low energy. With high-speed mode, existing applications deliver faster responses, richer engagement, and longer battery life. Bluetooth 5.3 enables fast, reliable firmware updates.

8.3.2 802.15.4 Thread, Zigbee, and 6LoWPAN

Through a dedicated IEEE radio API, the RF Core supports the 2.4GHz IEEE 802.15.4-2011 physical layer (2 Mchips per second Offset-QPSK with DSSS 1:8), used in Thread, Zigbee, and 6LoWPAN protocols. The 802.15.4 PHY and MAC are in radio and system ROM. TI also provides royalty-free protocol stacks for Thread and Zigbee as part of the SimpleLink SDK, enabling a robust end-to-end solution.

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8.4 Memory

1024kB nonvolatile (Flash) memory provides storage for code and data in two banks. The flash memory is insystem programmable and erasable. The last flash memory sector must contain a Customer Configuration section (CCFG) that is used by boot ROM and TI-provided drivers to configure the device. This configuration is done through the ccfg.c source file that is included in all TI-provided examples.

The ultra-low leakage system static RAM (SRAM) is split into up to eight 32kB blocks and can be used for both storage of data and execution of code. Retention of SRAM contents in Standby power mode is enabled by default and included in Standby mode power consumption numbers. Parity checking for detection of bit errors in memory is built-in, which reduces chip-level soft errors and thereby increases reliability. Parity can be disabled for an additional 32kB that can be allocated for general-purpose SRAM. System SRAM is always initialized to zeroes upon code execution from boot.

To improve code execution speed and lower power when executing code from nonvolatile memory, a 4-way nonassociative 8kB cache is enabled by default to cache and prefetch instructions read by the system CPU. The cache can be used as a general-purpose RAM by enabling this feature in the Customer Configuration Area (CCFG).

There is a 4kB ultra-low leakage SRAM available for use with the Sensor Controller Engine which is typically used for storing Sensor Controller programs, data, and configuration parameters. This RAM is also accessible by the system CPU. The Sensor Controller RAM is not cleared to zeroes between system resets.

The ROM includes a TI-RTOS kernel and low-level drivers, as well as significant parts of selected radio stacks, which free up flash memory for the application. The ROM also contains a serial (SPI and UART) bootloader that can be used for the initial programming of the device.

8.5 Sensor Controller

The Sensor Controller contains circuitry that can be selectively enabled in both Standby and Active power modes. The peripherals in this domain can be controlled by the Sensor Controller Engine, which is a proprietary power-optimized CPU. This CPU can read and monitor sensors or perform other tasks autonomously; thereby significantly reducing power consumption and offloading the system CPU.

The Sensor Controller Engine is user-programmable with a simple programming language that has syntax similar to C. This programmability allows for sensor polling and other tasks to be specified as sequential algorithms rather than the static configuration of complex peripheral modules, timers, DMA, register programmable state machines, or event routing.

The main advantages are:

- Flexibility—Data can be read and processed in unlimited manners while still ensuring ultra-low power.
- · 2MHz low-power mode enables the lowest possible handling of digital sensors
- · Dynamic reuse of hardware resources
- 40-bit accumulator supporting multiplication, addition, and shift
- · Observability and debugging options

Sensor Controller Studio is used to write, test, and debug code for the Sensor Controller. The tool produces C driver source code, which the System CPU application uses to control and exchange data with the Sensor Controller. Typical use cases may be (but are not limited to) the following:

Product Folder Links: CC2674R10

- Read analog sensors using integrated ADC or comparators
- Interface digital sensors using GPIOs, SPI, UART, or I²C (UART and I²C are bit-banged)
- · Capacitive sensing
- Waveform generation
- Very low-power pulse counting (flow metering)
- Key scan

The peripherals in the Sensor Controller include the following:

- The low-power clocked comparator can be used to wake the system CPU from any state in which the comparator is active. A configurable internal reference DAC can be used in conjunction with the comparator. The output of the comparator can also be used to trigger an interrupt or the ADC.
- Capacitive sensing functionality is implemented through the use of a constant current source, a time-to-digital
 converter, and a comparator. The continuous time comparator in this block can also be used as a higheraccuracy alternative to the low-power clocked comparator. The Sensor Controller takes care of baseline
 tracking, hysteresis, filtering, and other related functions when these modules are used for capacitive
 sensing.
- The ADC is a 12-bit 200ksps ADC with eight inputs and a built-in voltage reference. The ADC can be triggered by many different sources including timers, I/O pins, software, and comparators.
- The analog modules can connect to up to eight different GPIOs.
- · Dedicated SPI master with up to 6MHz clock speed.

The peripherals in the Sensor Controller can also be controlled from the main application processor.

8.6 Cryptography

The CC2674R10 device comes with a wide set of modern cryptography-related hardware accelerators, drastically reducing code footprint and execution time for cryptographic operations. It also has the benefit of being lower power and improves availability and responsiveness of the system because the cryptography operations runs in a background hardware thread.

Together with a large selection of open-source cryptography libraries provided with the software development kit (SDK), this allows for secure and future proof IoT applications to be easily built on top of the platform. The hardware accelerator modules are:

- True Random Number Generator (TRNG) module provides a true, nondeterministic noise source for the purpose of generating keys, initialization vectors (IVs), and other random number requirements. The TRNG is built on 24 ring oscillators that create unpredictable output to feed a complex nonlinear-combinatorial circuit.
- Secure Hash Algorithm 2 (SHA-2) with support for SHA224, SHA256, SHA384, and SHA512.
- Advanced Encryption Standard (AES) with 128-bit, 192-bit, and 256-bit key lengths.
- **Public Key Accelerator**—Hardware accelerator supporting mathematical operations needed for elliptic curves up to 512 bits.

Through use of these modules and the TI provided cryptography drivers, the following capabilities are available for an application or stack:

Key Agreement Schemes

- Elliptic Curve Diffie—Hellman with static or ephemeral keys (ECDH and ECDHE)
- Elliptic curve Password Authenticated Key Exchange by Juggling (ECJ-PAKE)

Signature Processing

- Elliptic curve Diffie-Hellman Digital Signature Algorithm (ECDSA)
- Edwards-curve Digital Signature Algorithm (EdDSA)

Curve Support

- Short Weierstrass form, such as:
 - NIST-P224 (secp224r1), NIST-P256 (secp256r1), NIST-P384 (secp384r1), NIST-P521 (secp521r1)

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- Brainpool-256R1, Brainpool-384R1, Brainpool-512R1
- Montgomery form, such as:
 - Curve25519
- Twisted Edwards form, such as:
 - Ed25519

Message Authentication Codes

- AEC CBC-MAC
- AES CMAC
- HMAC with SHA224, SHA256, SHA384, and SHA512
- Block cipher mode of operation

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- AES CCM and AES CCM-Star
- AES GCM
- AES ECB
- AES CBC
- AES CTR

Hash Algorithm

- SHA224
- SHA256
- SHA384
- SHA512

· True random number generation

Other capabilities, such as RSA encryption and signatures (using keys as large as 2048 bits) as well as other ECC curves such as Curve1174, can be implemented using the provided public key accelerator but are not part of the TI SimpleLink SDK for the CC2674R10 device.

8.7 Timers

A large selection of timers are available as part of the CC2674R10 device. These timers are:

Real-Time Clock (RTC)

A 70-bit 3-channel timer running on the 32kHz low-frequency system clock (SCLK_LF). This timer is available in all power modes except Shutdown. The timer can be calibrated to compensate for frequency drift when using the LF RCOSC as the low-frequency system clock. If an external LF clock with a frequency different from 32.768kHz is used, the RTC tick speed can be adjusted to compensate for this. When using TI-RTOS, the RTC is used as the base timer in the operating system and should thus only be accessed through the kernel APIs such as the Clock module. The real-time clock can also be read by the Sensor Controller Engine to timestamp sensor data and also has dedicated capture channels. By default, the RTC halts when a debugger halts the device.

General Purpose Timers (GPTIMER)

The four flexible GPTIMERs can be used as either 4×32 -bit timers or 8×16 -bit timers, all running on up to 48MHz. Each of the 16- or 32-bit timers supports a wide range of features such as one-shot or periodic counting, pulse width modulation (PWM), time counting between edges, and edge counting. The inputs and outputs of the timer are connected to the device event fabric, which allows the timers to interact with signals such as GPIO inputs, other timers, DMA, and ADC. The GPTIMERs are available in Active and Idle power modes.

Sensor Controller Timers

The Sensor Controller contains three timers:

The Sensor Controller contains three timers: AUX Timers 0 and 1 are 16-bit timers with a 2^N prescaler. Timers can either increment on a clock or each edge of a selected tick source. Both one-shot and periodical timer modes are available.

AUX Timer 2 is a 16-bit timer that can operate at 24MHz, 2MHz, or 32kHz independent of the Sensor Controller functionality. There are four capture or compare channels, which can be operated in one-shot or periodical modes. The timer can be used to generate events for the Sensor Controller Engine or the ADC, as well as for PWM output or waveform generation.

Radio Timer

A multichannel 32-bit timer running at 4MHz is available as part of the device radio. The radio timer is typically used as the timing base in wireless network communication using the 32-bit timing word as the network time. The radio timer is synchronized with the RTC by using a dedicated radio API when the device radio is turned on or off. This ensures that for a network stack, the radio timer seems to always be running when the radio is enabled. The radio timer is in most cases used indirectly through the trigger time fields in

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the radio APIs and should only be used when running the accurate 48MHz high-frequency crystal is the source of SCLK_HF.

Watchdog Timer

The watchdog timer is used to regain control if the system operates incorrectly due to software errors. It is typically used to generate an interrupt and reset the device for the case where periodic monitoring of the system components and tasks fails to verify proper functionality. The watchdog timer runs on a 1.5MHz clock rate and cannot be stopped once enabled. The watchdog timer continues to run in Standby power mode but pauses when a debugger halts the device.

Always On Watchdog Timer (AON_WDT)

The Always On Watchdog Timer is used during standby to regain control when the system has failed due to a software error or failure of an external device to respond in the expected way. It generates a reset when its configured time-out counter reaches zero and cannot be stopped once started, unless by asserting a device reset. The Always-on watchdog timer runs in Standby power mode and may pause when a debugger halts the device.

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8.8 Serial Peripherals and I/O

The SPI interface provides a standardized synchronous serial interface to communicate with devices compatible with SPI (3 and 4 wire), MICROWIRE and TI Synchronous Serial Format. The SPIs support master/slave operation up to 12MHz, programmable clock bit rate with prescaler, as well as configurable phase and polarity.

The UART interface implements universal asynchronous receiver and transmitter functions. The UART supports flexible baud-rate generation up to a maximum of 3Mbps with FIFO, multiple data sizes, stop, and parity bits as well as hardware handshake.

The I²S interface provides a standardized interface to exchange digital audio with devices compatible with this standard, including ADCs, DACs, and CODECs. The I²S can also receive pulse-density modulation (PDM) data from devices such as digital microphones and perform conversion to PCM data.

The I²C interface enables low-speed serial communications with devices compatible with the I²C standard. The I²C interface can handle both standard (100kHz) and fast (400kHz) speeds, as well as four modes of operation: master transmit/receive and slave transmit/receive.

The I/O controller (IOC) controls the digital I/O pins and contains multiplexer circuitry to allow a set of peripherals to be assigned to I/O pins in a flexible manner. All digital I/Os are interrupt and wake-up capable, have a programmable pullup and pulldown function, and can generate an interrupt on a negative or positive edge (configurable). When configured as an output, pins can function as either push-pull or open-drain. Five GPIOs have high-drive capabilities, which are marked in **bold** in セクション 6. All digital peripherals can be connected to any digital pin on the device.

8.9 Battery and Temperature Monitor

A combined temperature and battery voltage monitor is available in the CC2674R10 device. The battery and temperature monitor allows an application to continuously monitor on-chip temperature and supply voltage and respond to changes in environmental conditions as needed. The module contains window comparators to interrupt the system CPU when temperature or supply voltage goes outside defined windows. These events can also be used to wake up the device from Standby mode through the always-on (AON) event fabric.

8.10 µDMA

The device includes a direct memory access (μ DMA) controller. The μ DMA controller provides a way to offload data-transfer tasks from the system CPU, thus allowing for more efficient use of the processor and the available bus bandwidth. The μ DMA controller can perform a transfer between memory and peripherals. The μ DMA controller has dedicated channels for each supported on-chip module and can be programmed to automatically perform transfers between peripherals and memory when the peripheral is ready to transfer more data.

Some features of the µDMA controller include the following (this is not an exhaustive list):

- Highly flexible and configurable channel operation of up to 32 channels
- Transfer modes: memory-to-memory, memory-to-peripheral, peripheral-to-memory, and peripheral-to-peripheral
- Data sizes of 8 bits, 16 bits, and 32 bits
- · Ping-pong mode for continuous streaming of data

8.11 Debug

The debug subsystem implements two IEEE standards for debug and test purposes:

IEEE 1149.7 Class 4: Reduced-pin and Enhanced-functionality Test Access Port and Boundary-scan Architecture. This is known by the acronym cJTAG (compact JTAG) and this device uses only two pins to communicate with the target: TMS (JTAG_TMSC) and TCK (JTAG_TCKC). This is the default mode of operation.

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IEEE standard 1149.1: Test Access Port and Boundary Scan Architecture Test Access Port (TAP). This standard is known by the acronym JTAG and this device uses four pins to communicate with the target: TMS (JTAG TMSC), TCK (JTAG TCKC), TDI (JTAG TDI), and TDO (JTAG TDO).

The debug subsystem also implements a user-configurable firewall to control unauthorized access to debug/test ports.

Also featured is **EnergyTrace/EnergyTrace++**. This technology implements an improved method for measuring MCU current consumption, which features a very high dynamic range (from sub-µA to hundreds of mA), high sample rate (up to 256 kSamples/s), and the ability to track the CPU and peripheral power states.

Two modes of operation can be configured. **EnergyTrace** measures the overall MCU current consumption and allows maximum accuracy and speed to track ultra-low-power states as well as the fast power transitions during radio transmission and reception. **EnergyTrace++** tracks the various power states of both the CPU and its Peripherals as well as the system clocks, allowing close monitoring of the overall device activity.

8.12 Power Management

To minimize power consumption, the CC2674R10 supports a number of power modes and power management features (see 表 8-1).

MODE	SOFTV	RESET PIN				
WIODE	ACTIVE	IDLE	STANDBY	SHUTDOWN	HELD	
CPU	Active	Off	Off	Off	Off	
Flash	On	Available	Off	Off	Off	
SRAM	On	On	Retention	Off	Off	
Supply System	On	On	Duty Cycled	Off	Off	
Register and CPU retention	Full	Full	Partial	No	No	
SRAM retention	Full	Full	Full	No	No	
48MHz high-speed clock (SCLK_HF)	or RCOSC_HF	or RCOSC_HF	Off	Off	Off	
2MHz medium-speed clock (SCLK_MF)	RCOSC_MF	RCOSC_MF	Available	Off	Off	
32kHz low-speed clock (SCLK_LF)	XOSC_LF or RCOSC_LF	XOSC_LF or RCOSC_LF	XOSC_LF or RCOSC_LF	Off	Off	
Peripherals	Available	Available	Off	Off	Off	
Sensor Controller	Available	Available	Available	Off	Off	
Wake-up on RTC	Available	Available	Available	Off Available	Off Off	
Wake-up on pin edge	Available	Available	Available			
Wake-up on reset pin	On	On	On	On	On	
Brownout detector (BOD)	On	On	Duty Cycled	Off	Off	
Power-on reset (POR)	On	On	On	Off	Off	
Watchdog timer (WDT)	Available	Available	Paused	Off	Off	
Always-on Watchdog timer (AON_WDT)	Available	Available	Available	Off	Off	

表 8-1. Power Modes

In **Active** mode, the application system CPU is actively executing code. Active mode provides normal operation of the processor and all of the peripherals that are currently enabled. The system clock can be any available clock source (see 表 8-1).

In **Idle** mode, all active peripherals can be clocked, but the Application CPU core and memory are not clocked and no code is executed. Any interrupt event brings the processor back into active mode.

English Data Sheet: SWRS268



In **Standby** mode, only the always-on (AON) domain is active. An external wake-up event, RTC event, or Sensor Controller event is required to bring the device back to active mode. MCU peripherals with retention do not need to be reconfigured when waking up again, and the CPU continues execution from where it went into standby mode. All GPIOs are latched in standby mode.

In **Shutdown** mode, the device is entirely turned off (including the AON domain and Sensor Controller), and the I/Os are latched with the value they had before entering shutdown mode. A change of state on any I/O pin defined as a *wake from shutdown pin* wakes up the device and functions as a reset trigger. The CPU can differentiate between reset in this way and reset-by-reset pin or power-on reset by reading the reset status register. The only state retained in this mode is the latched I/O state and the flash memory contents.

The Sensor Controller is an autonomous processor that can control the peripherals in the Sensor Controller independently of the system CPU. This means that the system CPU does not have to wake up, for example, to perform an ADC sampling or poll a digital sensor over SPI, thus saving both current and wake-up time that would otherwise be wasted. The Sensor Controller Studio tool enables the user to program the Sensor Controller, control its peripherals, and wake up the system CPU as needed. All Sensor Controller peripherals can also be controlled by the system CPU.

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The power, RF, and clock management for the CC2674R10 device require specific configuration and handling by software for optimized performance. This configuration and handling is implemented in the TI-provided drivers that are part of the CC2674R10 software development kit (SDK). Therefore, TI highly recommends using this software framework for all application development on the device. The complete SDK with TI-RTOS (optional), device drivers, and examples is offered free of charge in the source code.

8.13 Clock Systems

The CC2674R10 device has several internal system clocks.

SCLK_MF is an internal 2MHz clock that is used by the Sensor Controller in low-power mode and also for internal power management circuitry. The SCLK_MF clock is always driven by the internal 2MHz RC oscillator (RCOSC MF).

SCLK_LF is the 32.768kHz internal low-frequency system clock. It can be used by the Sensor Controller for ultra-low-power operation and is also used for the RTC and to synchronize the radio timer before or after Standby power mode. SCLK_LF can be driven by the internal 32.8kHz RC Oscillator (RCOSC_LF), a 32.768kHz watch-type crystal, or a clock input on any digital IO.

When using a crystal or the internal RC oscillator, the device can output the 32kHz SCLK_LF signal to other devices, thereby reducing the overall system cost.

8.14 Network Processor

Depending on the product configuration, the CC2674R10 device can function as a wireless network processor (WNP), a device running the wireless protocol stack with the application running on a separate host MCU, or as a system-on-chip (SoC) with the application and protocol stack running on the system CPU inside the device.

In the first case, the external host MCU communicates with the device using SPI or UART. In the second case, the application must be written according to the application framework supplied with the wireless protocol stack.

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9 Application, Implementation, and Layout

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Information in the following Applications section is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

For general design guidelines and hardware configuration guidelines, refer to CC13xx/CC26xx Hardware Configuration and PCB Design Considerations Application Report.

9.1 Reference Designs

The following reference designs should be followed closely when implementing designs using the CC2674R10 device.

Special attention must be paid to RF component placement, decoupling capacitors, and DC/DC regulator components, as well as ground connections for all of these.

CC1352REM-XD7793-XD24 Design Files The CC1352REM-XD7793-XD24 reference design provides schematic, layout, and production files for the characterization board used for deriving the performance number found in this document.

CC26x2REM-7ID Design Files

The CC26x2REM-7ID reference design provides schematic, layout, and production files for the characterization board used for deriving the performance number found in this document.

LP-EM-CC1354P10-1 Design Files

Detailed schematics and layouts for the multiband CC1354P10 LaunchPad evaluation board featuring 868/915MHz RF matching on the 20dBm PA output and up to 5dBm TX power at 2.4GHz.

LP-EM-CC1354P10-6 Design Files

Detailed schematics and layouts for the multiband CC1354P10 LaunchPad evaluation board featuring 2.4GHz RF matching optimized for 10dBm operation on the 20dBm PA output and up to 13dBm TX power at 433MHz.

Sub-1 GHz and 2.4 GHz Antenna Kit for LaunchPad™ Development Kit and SensorTag The antenna kit allows real-life testing to identify the optimal antenna for your application. The antenna kit includes 16 antennas for frequencies from 169MHz to 2.4GHz, including:

- PCB antennas
- Helical antennas
- · Chip antennas
- Dual-band antennas for 868MHz and 915MHz combined with 2.4GHz

The antenna kit includes a JSC cable to connect to the Wireless MCU LaunchPad Development Kits and SensorTags.

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10 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed as follows.

10.1 Tools and Software

The CC2674R10 device is supported by a variety of software and hardware development tools.

Development Kit

CC1354P10-6 LaunchPad™ Development Kit

The CC1354P10-6 LaunchPad [™] Development Kit enables the development of high-performance wireless applications in the 863MHz to 930MHz and 2.4GHz frequency bands that benefit from low-power operation. The kit features the CC1354P10 multiband and multiprotocol SimpleLink [™] Wireless MCU with an integrated High-Power Amplifier. The kit works with the LaunchPad ecosystem, easily enabling additional functionality like sensors, displays, and more. The built-in EnergyTrace [™] software is an energy-based code analysis tool that measures and displays the application's energy profile and helps to optimize it for ultra-low power consumption.

The RF configuration of the LaunchPad enables up to +14dBm output power for 863MHz to 930MHz and +20dBm output power for 2.4GHz.

LP-XDS110 LaunchPad™ Debug Probe

The LP-XDS110 LaunchPad ™ Debug Probe enables the development of high-performance wireless applications in the entire family of LP-EM LaunchPad ™ development boards. Featuring a seamless connection with the new 20-pin LP-EM Debug connector, it supports not only multiple standards such as JTAG/cJTAG/SWD but also a UART backchannel for maximum debugging flexibility. It also features an Arm® 10-pin Debug connector to perform debugging on any custom board.

LP-XDS110ET LaunchPad™ Debug Probe

The LP-XDS110ET LaunchPad ™ Debug Probe enables the development of high-performance wireless applications in the entire family of LP-EM LaunchPad ™ development boards. Featuring a seamless connection with the new 20-pin LP-EM Debug connector, it supports not only multiple standards such as JTAG/cJTAG/SWD but also a UART backchannel for maximum debugging flexibility. In addition, it also features an Arm® 10-pin Debug connector to perform debugging on any custom board. This Debug Probe also features the XDS110 EnergyTrace™ technology, which is a new method for measuring the current consumption that captures the complete operational profile of the wireless MCU.

TMDSEMU110-U Debug Probe

The TMDSEMU110-U Debug Probe enables the development of high-performance wireless applications in the entire family of SimpleLink™ LaunchPad™ development boards. Featuring a convenient enclosure, which grants the proper mechanical robustness for field and production environments, it supports not only multiple standards such as JTAG/cJTAG/SWD but also a UART backchannel and four GPIOs for maximum debugging flexibility. In addition, the expansion connector allows using the TMDSEMU110-ETH add-on (sold separately), which adds the full-featured XDS110 EnergyTrace™ technology with variable supply voltage from 1.8V to 3.6V and up to 800mA of supply current. The XDS110 EnergyTrace™ technology is a new method for measuring the current consumption that captures the complete operational profile of the wireless MCU.

Software

SimpleLink™ LOWPOWER F2 SDK

The SimpleLink™ LOWPOWER F2 Software Development Kit (SDK) provides a complete package for the development of wireless applications on the CC13XX / CC26XX family of



devices. The SDK includes a comprehensive software package for the CC2674R10 device, including the following protocol stacks:

- Bluetooth Low Energy 4 and 5.3
- Thread (based on OpenThread)
- TI Z-Stack (Zigbee 3.0)
- TI 15.4-Stack—an IEEE 802.15.4-based star networking solution for Sub-1GHz and 2.4GHz
- EasyLink a large set of building blocks for building proprietary RF software stacks
- Multiprotocol support—concurrent operation between stacks using the Dynamic Multiprotocol Manager (DMM)
- TI Wi-SUN FAN Stack
- Matter

The SimpleLink™ LOWPOWER F2 SDK is part of TI's SimpleLink™ MCU platform, offering a single development environment that delivers flexible hardware, software, and tool options for customers developing wired and wireless applications. For more information about the SimpleLink[™] MCU Platform, visit ti.com/simplelink.

Development Tools

Code Composer Studio™ Integrated Development **Environment** (IDE)

Code Composer Studio is an integrated development environment (IDE) that supports TI's Microcontroller and Embedded Processors portfolio. Code Composer Studio comprises a suite of tools used to develop and debug embedded applications. It includes an optimizing C/C++ compiler, source code editor, project build environment, debugger, profiler, and many other features. The intuitive IDE provides a single user interface taking you through each step of the application development flow. Familiar tools and interfaces allow users to get started faster than ever before. Code Composer Studio combines the advantages of the Eclipse® software framework with advanced embedded debug capabilities from TI resulting in a compelling feature-rich development environment for embedded developers.

CCS has support for all SimpleLink™ Wireless MCUs and includes support for EnergyTrace ™ software (application energy usage profiling). A real-time object viewer plugin is available for TI-RTOS, part of the SimpleLink™ SDK.

Code Composer Studio is provided free of charge when used in conjunction with the XDS debuggers included on a LaunchPad Development Kit.

Code Composer Studio™ Cloud IDE

Code Composer Studio (CCS) Cloud is a web-based IDE that allows you to create, edit, and build CCS and Energia™ projects. After you have successfully built your project, you can download and run on your connected LaunchPad. Basic debugging, including features like setting breakpoints and viewing variable values, is now supported with CCS Cloud.

IAR Embedded Workbench® for **Arm**®

IAR Embedded Workbench® is a set of development tools for building and debugging embedded system applications using Assembler, C, and C++. It provides a completely integrated development environment that includes a project manager, editor, and build tools. IAR has support for all SimpleLink™ Wireless MCUs. It offers broad debugger support, including XDS110, IAR I-jet[™], and Segger J-Link[™]. A real-time object viewer plugin is available for TI-RTOS, part of the SimpleLink™ SDK. IAR is also supported out-of-the-box on most software examples provided as part of the SimpleLink™ SDK.

A 30-day evaluation or a 32kB size-limited version is available through iar.com.

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SmartRF™ Studio SmartRF™ Studio 7 is a Windows® application that can be used to evaluate and configure SimpleLink™ Wireless MCUs from Texas Instruments. The application will help designers of RF systems to easily evaluate the radio at an early stage in the design process. It is



especially useful for the generation of configuration register values and for practical testing and debugging of the RF system. SmartRF Studio can be used either as a standalone application or together with applicable evaluation boards or debug probes for the RF device. Features of the SmartRF Studio include:

- Link tests—send and receive packets between nodes
- Antenna and radiation tests—set the radio in continuous wave TX and RX states
- Export radio configuration code for use with the TI SimpleLink™ SDK RF driver
- Custom GPIO configuration for signaling and control of external switches

Sensor Controller Studio

Sensor Controller Studio is used to write, test, and debug code for the Sensor Controller peripheral. The tool generates a Sensor Controller Interface driver, which is a set of C source files that are compiled into the System CPU application. These source files also contain the Sensor Controller binary image and allow the System CPU application to control and exchange data with the Sensor Controller. Features of the Sensor Controller Studio include:

- Ready-to-use examples for several common use cases
- Full toolchain with built-in compiler and assembler for programming in a C-like programming language
- Provides rapid development by using the integrated sensor controller task testing and debugging functionality, including visualization of sensor data and verification of algorithms

UniFlash

UniFlash is a standalone tool used to program on-chip flash memory on TI MCUs. UniFlash has a GUI, command line, and scripting interface. UniFlash is available free of charge.

10.1.1 SimpleLink™ Microcontroller Platform

The SimpleLink™ microcontroller platform sets a new standard for developers with the broadest portfolio of wired and wireless Arm® MCUs (System-on-Chip) in a single software development environment. Delivering flexible hardware, software and tool options for your IoT applications. Invest once in the SimpleLink™ software development kit and use throughout your entire portfolio. Learn more on ti.com/simplelink.

10.2 Documentation Support

To receive notification of documentation updates on data sheets, errata, application notes and similar, navigate to the device product folder on ti.com/product/CC2674R10. In the upper right corner, click on Alert me to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

The current documentation that describes the MCU, related peripherals, and other technical collateral is listed as follows.

TI Resource Explorer

TI Resource Explorer Software examples, libraries, executables, and documentation are available for your device and development board.

Errata

CC2674R10 Silicon Errata

The silicon errata describes the known exceptions to the functional specifications for each silicon revision of the device and description on how to recognize a device revision.

Application Reports

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All application reports for the CC2674R10 device are found on the device product folder at: ti.com/product/CC2674R10/technicaldocuments.

Technical Reference Manual (TRM)

CC13x4, CC26x4 SimpleLink™ Wireless MCU Technical Reference Manual

The TRM provides detailed descriptions of all modules and peripherals available in the device family.

10.3 サポート・リソース

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10.6 用語集

テキサス・インスツルメンツ用語集 この用語集には、用語や略語の一覧および定義が記載されています。



11 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Changes from June 20, 2023 to April 30, 2024 (from Revision A (June 2023) to Revision B						
(/	April 2024))	Page				
•	RSK パッケージの暫定情報の脚注を削除。	1				
•	Updated Device Comparison table	<mark>5</mark>				
•	Updated Sensor controller power consumption in セクション 7.5, Power Consumption - Power Modes	13				
•	Updated Flash specifications in セクション 7.7, Nonvolatile (Flash) Memory Characteristics	13				
•	Updated graphs and tables on Typical characteristics	34				
•	Added EnergyTrace information to セクション 8.11, <i>Debug</i>	46				

Product Folder Links: CC2674R10



12 Mechanical, Packaging, and Orderable Information

12.1 Packaging Information

The following pages include mechanical packaging and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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Product Folder Links: CC2674R10

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PACKAGING INFORMATION

Orderable part number	Status (1)	Material type	Package Pins	Package qty Carrier	RoHS	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
CC2674R106T0RGZR	Active	Production	VQFN (RGZ) 48	2500 LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 105	CC2674 R106
CC2674R106T0RGZR.B	Active	Production	VQFN (RGZ) 48	2500 LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 105	CC2674 R106
CC2674R106T0RSKR	Active	Production	VQFN (RSK) 64	2000 LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 105	CC2674 R106
CC2674R106T0RSKR.B	Active	Production	VQFN (RSK) 64	2000 LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 105	CC2674 R106

⁽¹⁾ Status: For more details on status, see our product life cycle.

- (3) RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.
- (4) Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.
- (5) MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.
- (6) Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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⁽²⁾ Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.



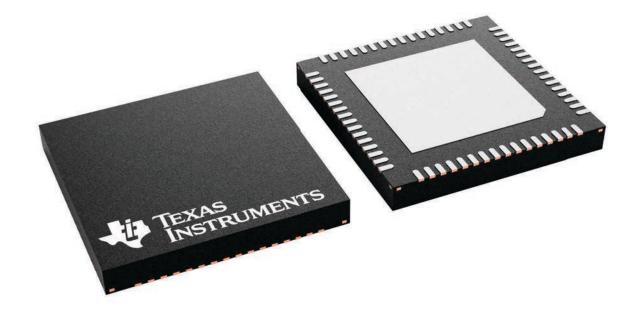
PACKAGE OPTION ADDENDUM

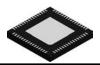
www.ti.com 8-Nov-2025

8 x 8, 0.4 mm pitch

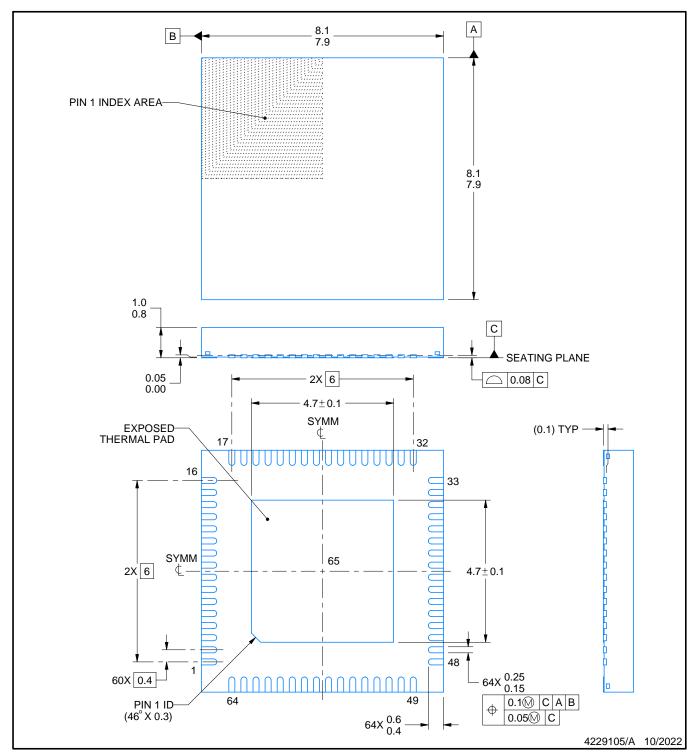
PLASTIC QUAD FLATPACK - NO LEAD

This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.





PLASTIC QUAD FLATPACK - NO LEAD

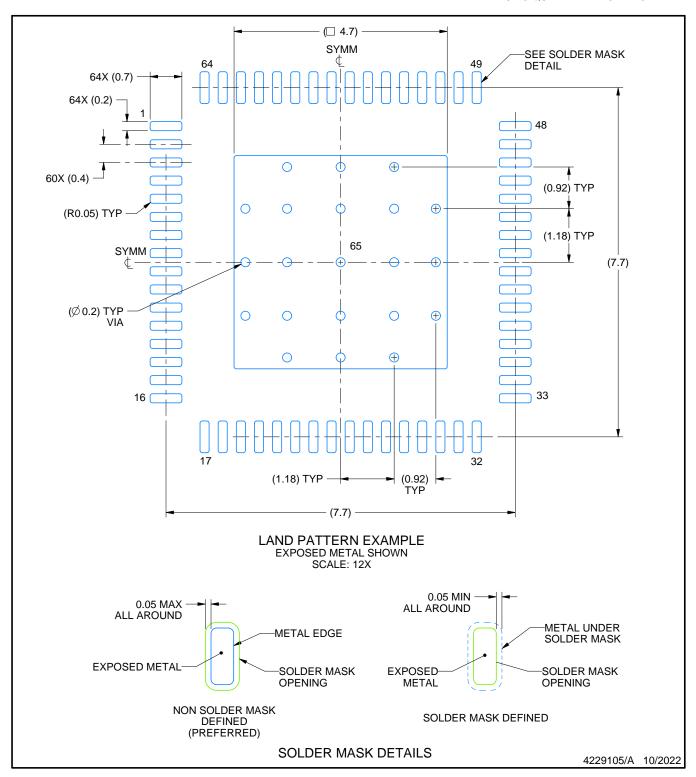


NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.



PLASTIC QUAD FLATPACK - NO LEAD

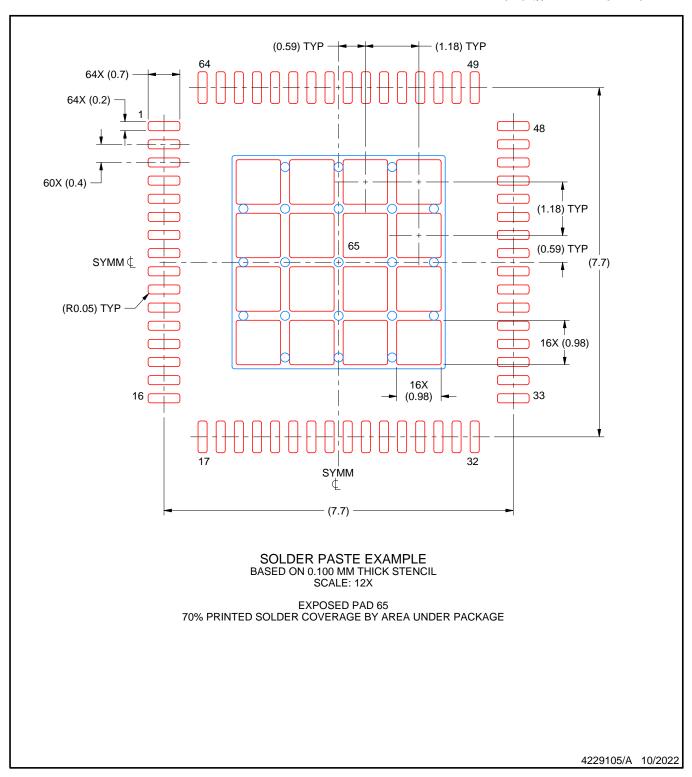


NOTES: (continued)

- 4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- 5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



PLASTIC QUAD FLATPACK - NO LEAD



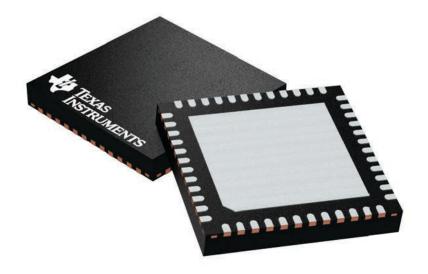
NOTES: (continued)

^{6.} Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



7 x 7, 0.5 mm pitch

PLASTIC QUADFLAT PACK- NO LEAD

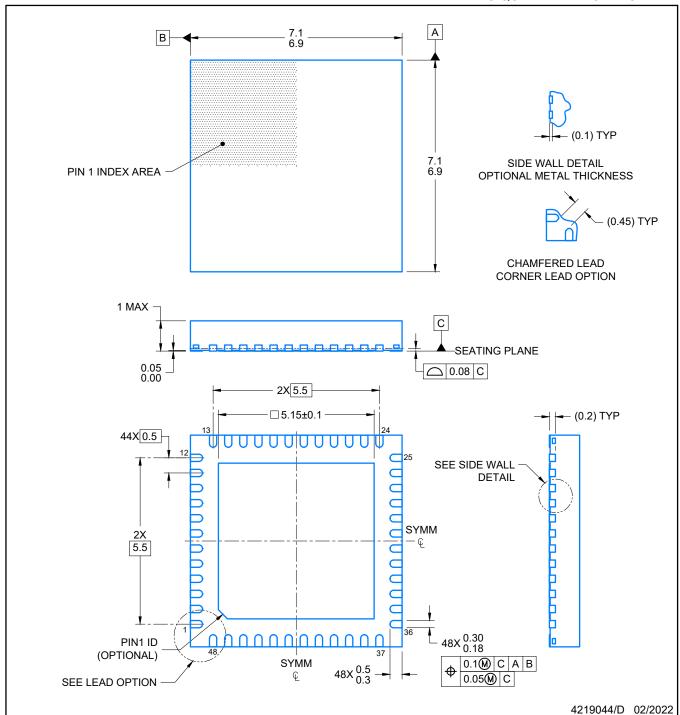


Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.

4224671/A



PLASTIC QUADFLAT PACK- NO LEAD

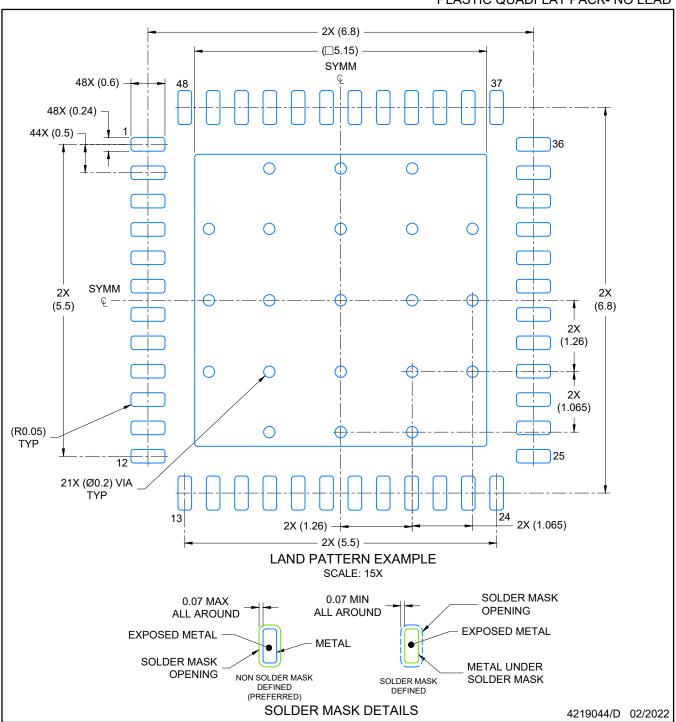


NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for optimal thermal and mechanical performance.



PLASTIC QUADFLAT PACK- NO LEAD

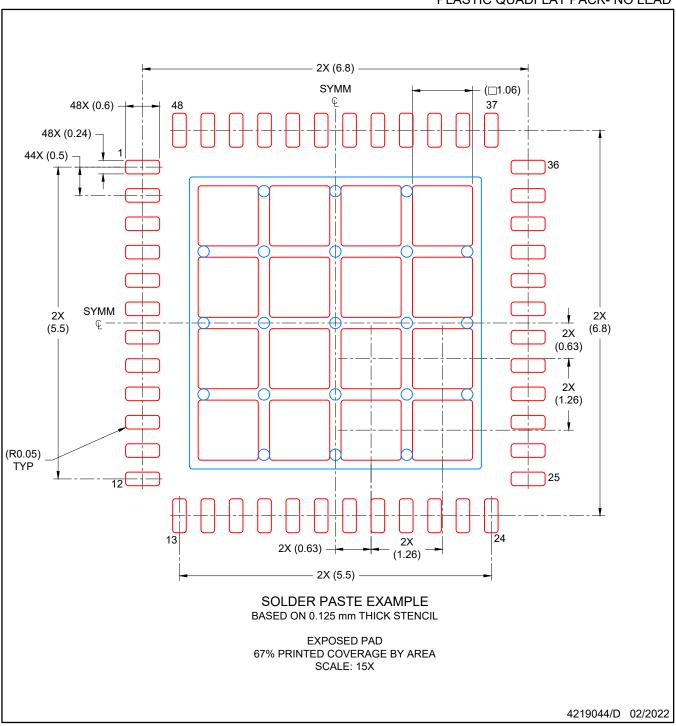


NOTES: (continued)

- 4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- 5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



PLASTIC QUADFLAT PACK- NO LEAD



NOTES: (continued)

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